

Hydrogen Storage in Graphene

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National Enterprise for nanoScience and nanoTechnology

NEST

Outline

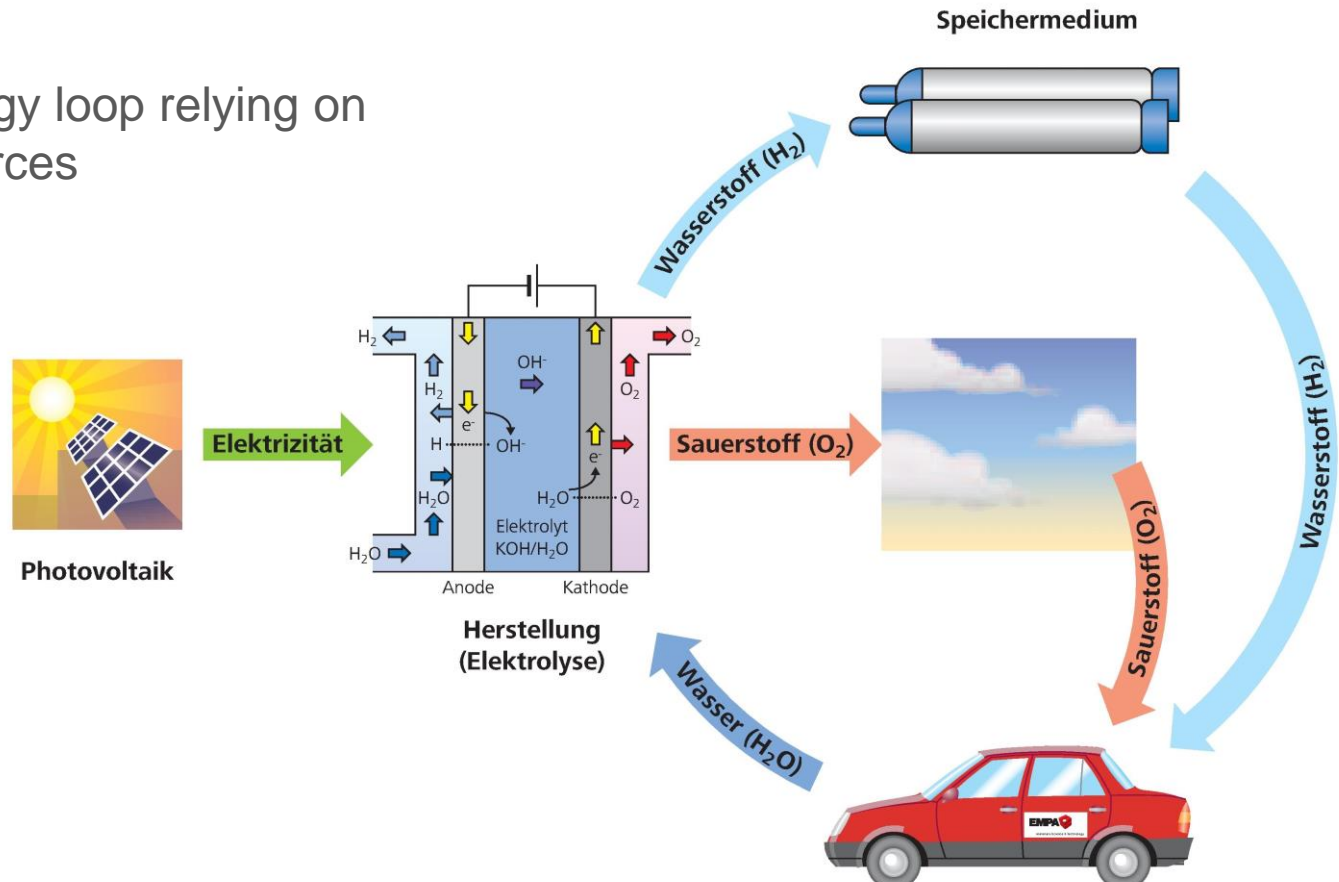
- Introduction to Hydrogen Storage
- Epitaxial Graphene
- Hydrogen Storage by Corrugation
(Chemisorption)
- Hydrogen Storage by Functionalization
(Physisorption)

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Hydrogen Life Cycle

Complete energy loop relying on renewable sources



Hydrogen Storage in a safe and cheap way is
a critical issue

Hydrogen-fuelled vehicles



Hydrogen-fuelled vehicles



Fuel Cell Vehicle

A vehicle running
on hydrogen



Sales launch of Fuel Cell sedan in Japan before April 2015

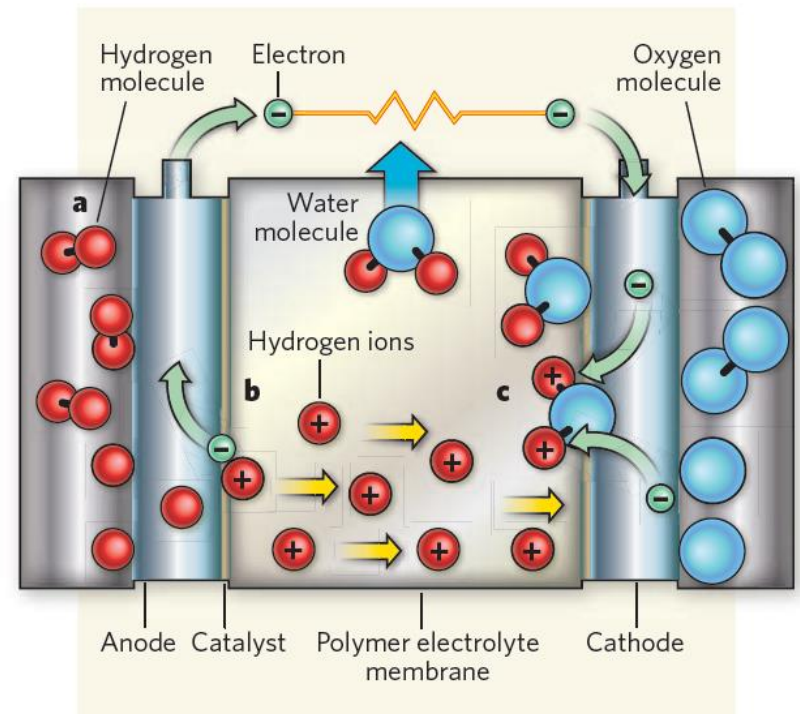


Hydrogen & energy

As a **fuel**, hydrogen has advantages:


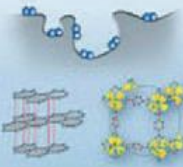
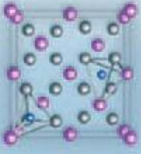

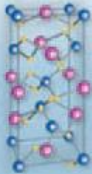
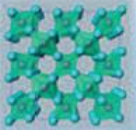

- Highest energy-to-mass ratio
- $\text{H}_2 + 1/2 \text{O}_2 \rightarrow \text{H}_2\text{O} \quad \Delta H = -2.96\text{eV}$
- Non-toxic and “clean” (product = water)
- Renewable, unlimited resource
- Reduction in CO_2 emission
- Reduction of oil dependency

However, hydrogen is NOT an **energy source**: it must be produced e.g. by electrolysis, needing +2.96 eV, with zero balance with respect to energy production.



Hydrogen fuel cell

Hydrogen Storage

						
Liquid hydrogen	Cryo-adsorption	Interstitial metal hydride	Compressed hydrogen	Aluminate	Salt-like metal hydride	Water
LH2	Activated carbon	Laves Phase Comp./ FeTiH _x / LaNi ₅ H _x	CGH2	NaAlH ₄	MgH ₂	H ₂ O
100 mat.wt%	6.5 mat.wt%	2 mat.wt%	100 mat.wt%	5.5 mat.wt%	7.5 mat.wt%	11 mat.wt%
Operating temperature						
-253°C	> -200°C	0 - 30°C	25°C	70 - 170°C	330°C	>> 1000°C

Targets for **transport applications** not reached yet:

$$\rho_m > 5.5 \text{ wt\%}$$

$$\rho_v > 50 \text{ kg H}_2 / \text{m}^3$$

$$P_{eq} \approx 1 \text{ bar at } T < 100^\circ\text{C}$$

Compressed H₂:

High pressure and heavy container to support such pressure

Solid State:

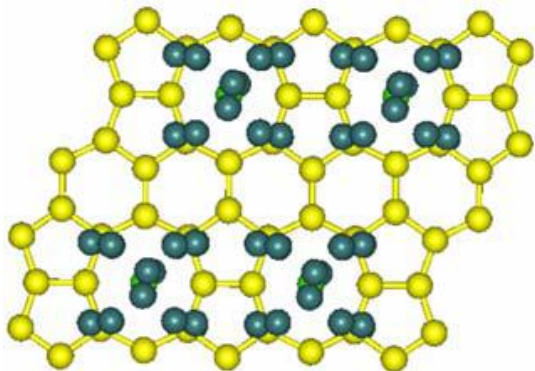
Physisorption
Chemisorption

Liquid H₂:

Liquefaction needs energy and consumes more than 20% of the recoverable energy

Graphene for hydrogen storage

- Graphene is lightweight, inexpensive, robust, chemically stable
- Large surface area ($\sim 2600 \text{ m}^2/\text{g}$)
- Functionalized graphene has been predicted to adsorb up to 9 wt% of hydrogen

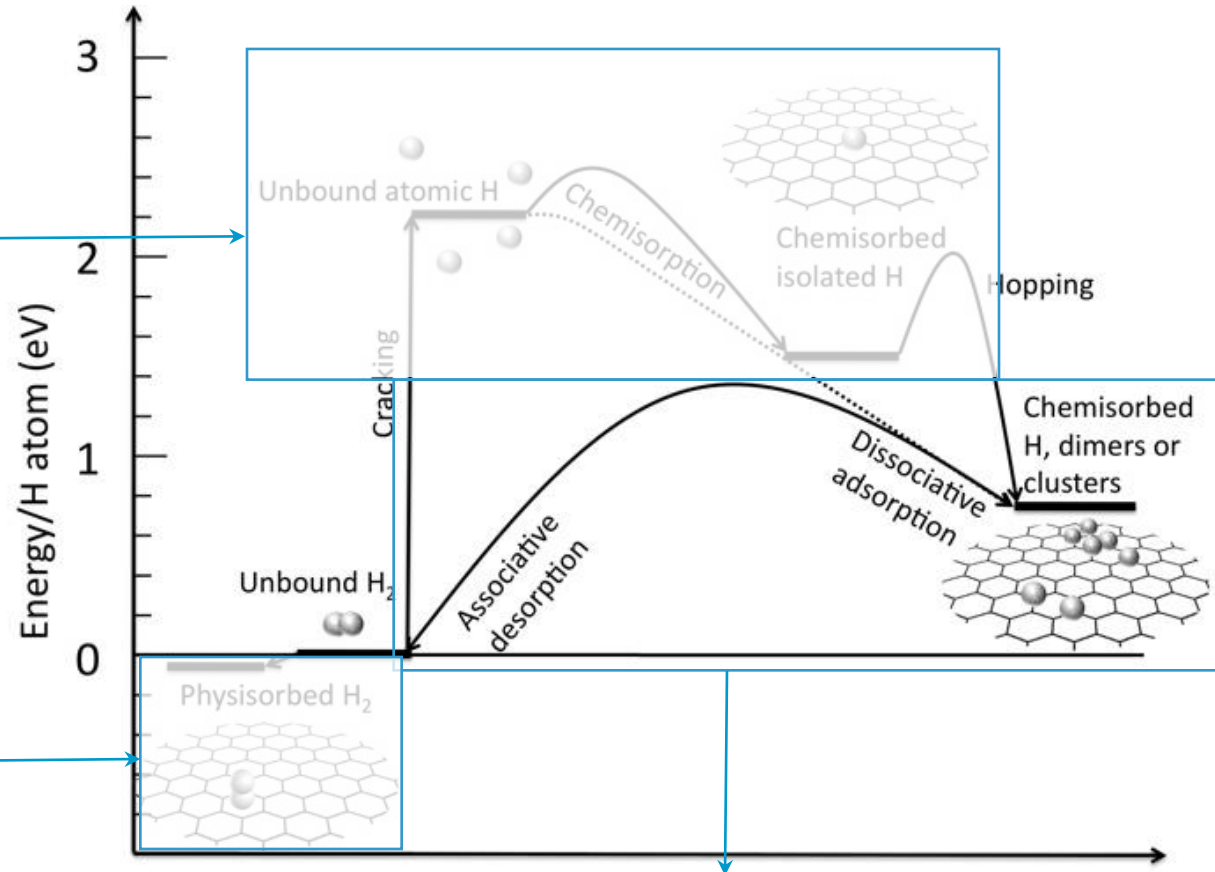


Yang et al., PRB 79 (2009) 075431

H storage in graphene

❖ Atomic hydrogen chemisorption has a small or negligible chemisorption barrier \Rightarrow feasible but H_2 must be cracked

❖ Physisorption weakly binds hydrogen \Rightarrow acceptable storage densities only at low temperatures and/or high pressure

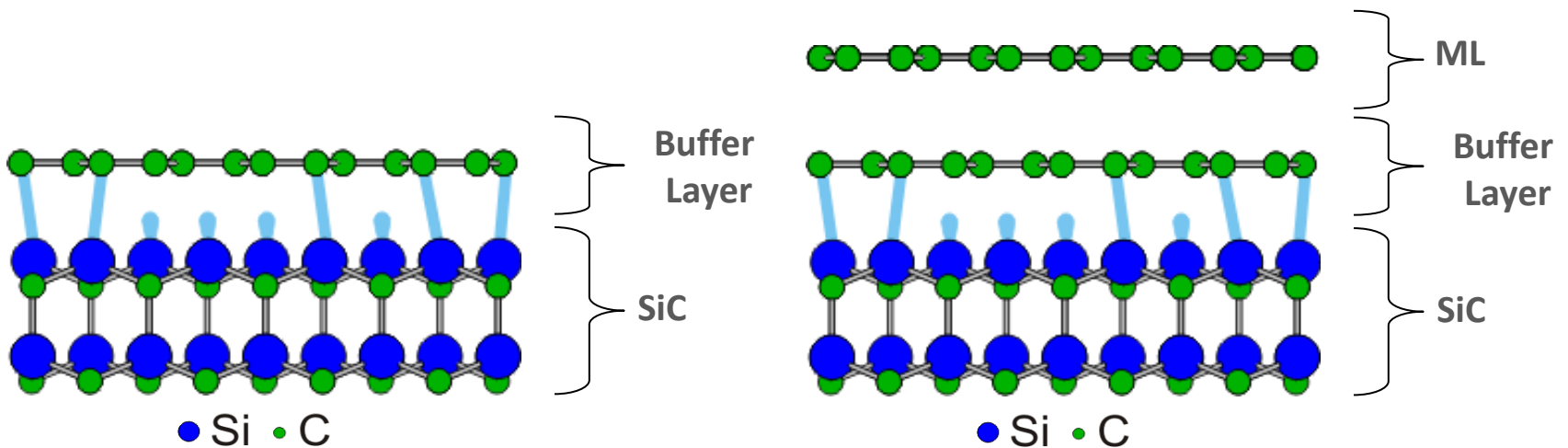


❖ Molecular hydrogen chemi(de)sorption has high barrier (theoretical estimate $\sim eV$) \Rightarrow chemisorbed H is stable for transportation etc, but catalytic mechanisms are necessary in the loading-release phases

Outline

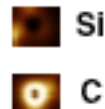
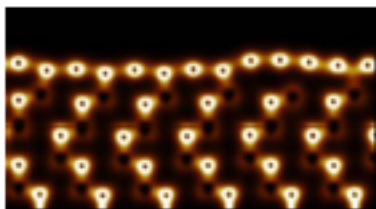
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Graphene growth on SiC(0001)



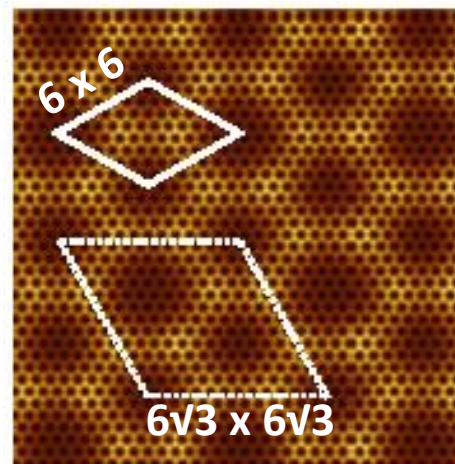
Buffer Layer

Topologically identical atomic carbon structure as graphene. Does not have the electronic band structure of graphene due to periodic sp^3 C-Si bonds.



F. Varchon, et al., PRB 77, 235412 (2008).

Theoretical Calculations



F. Varchon, et al., PRB 77, 235412 (2008).

Superstructure of both the buffer layer and monolayer graphene on the Si face from the periodic interaction with the substrate.

Buffer Layer

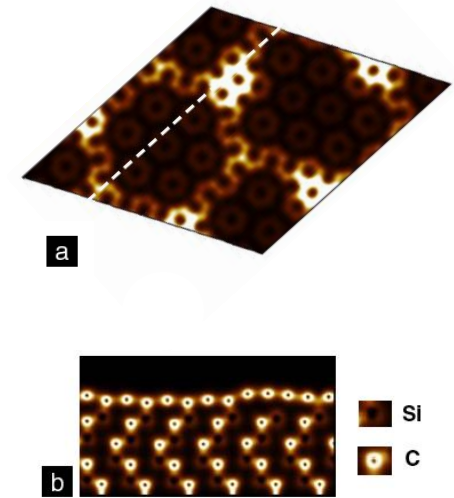
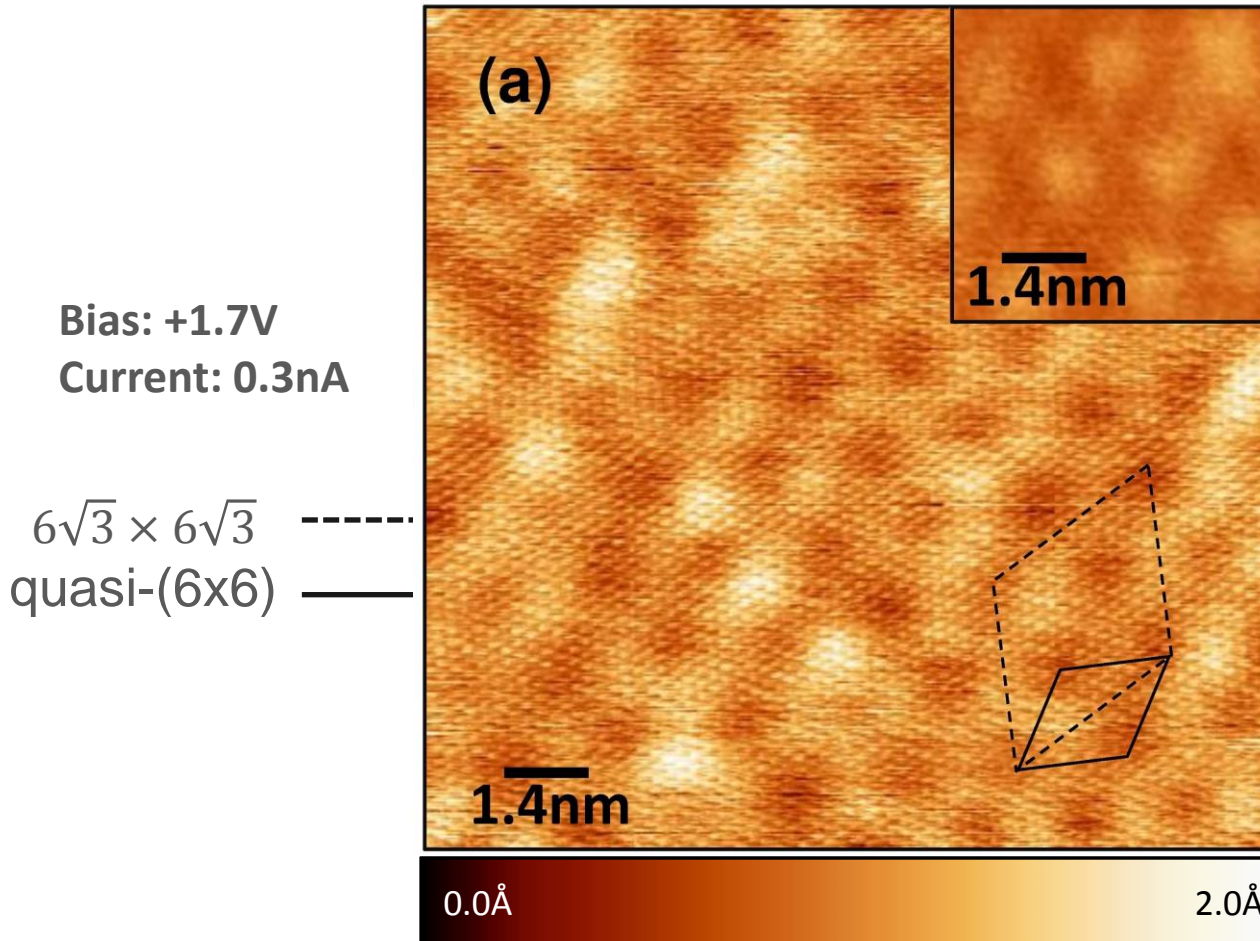
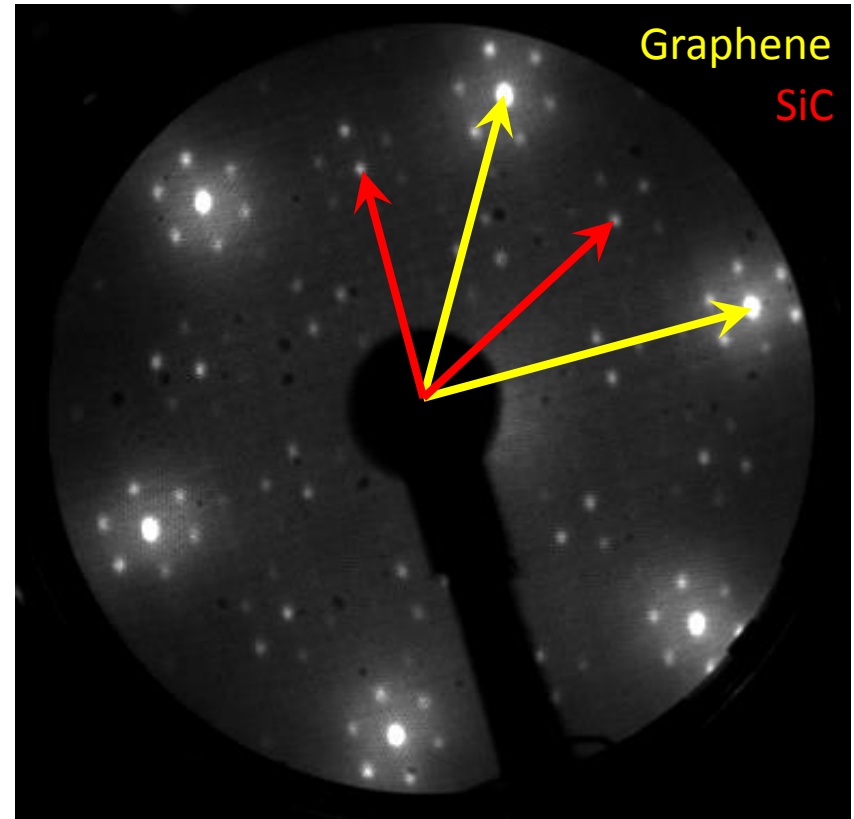
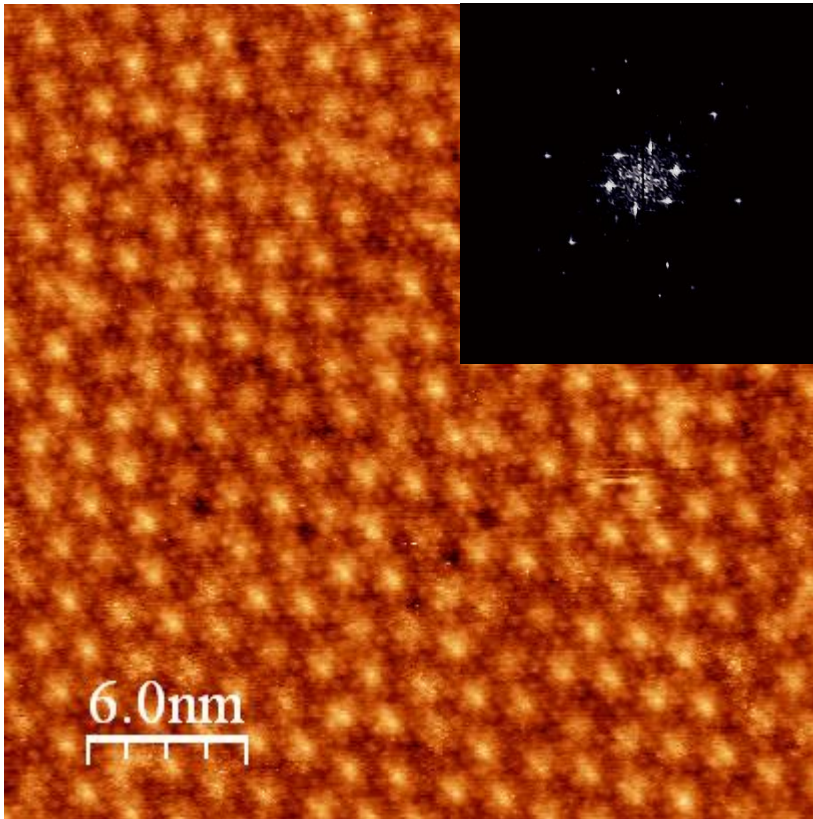


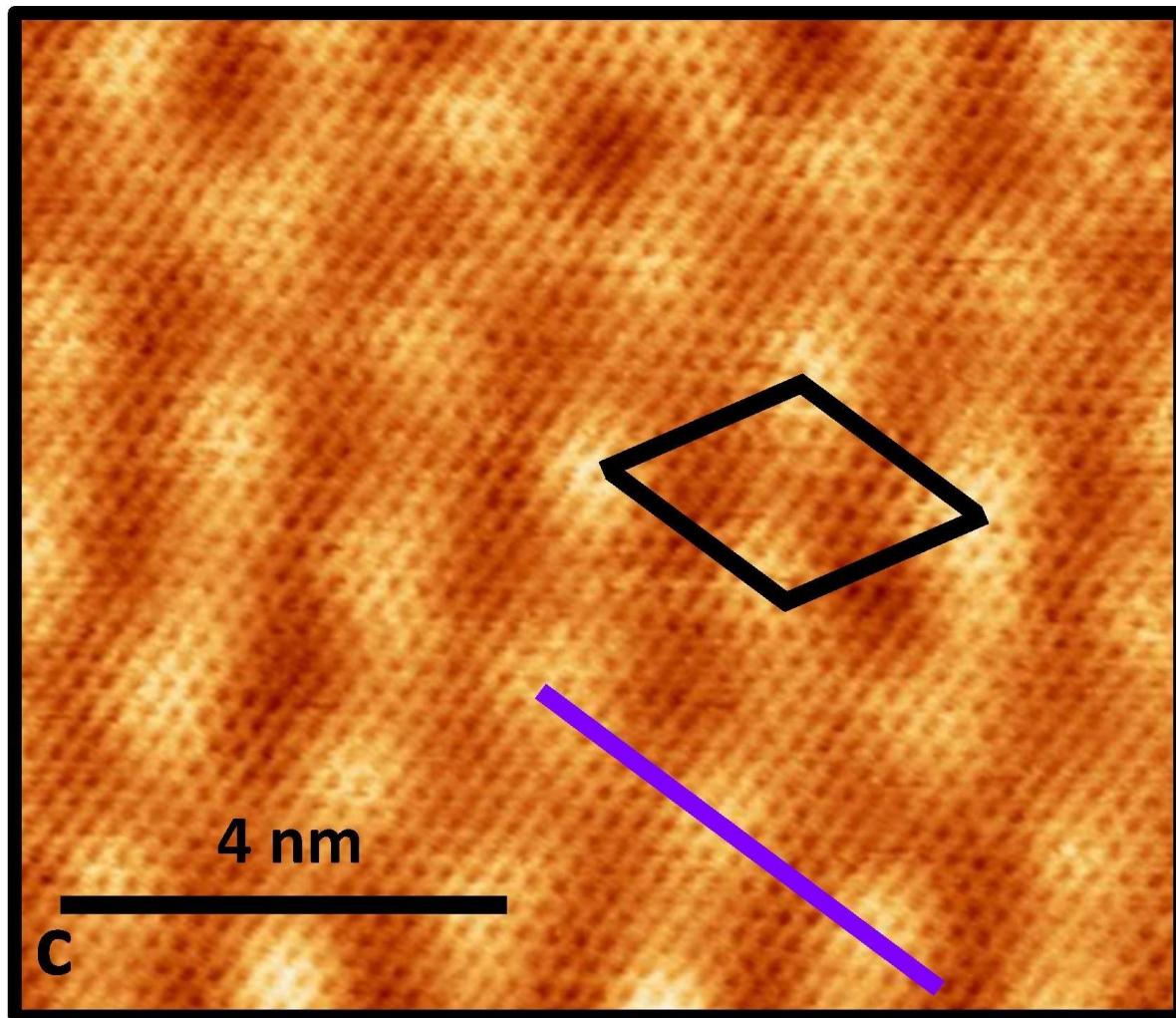
FIG. 2. (Color online) Total charge density of the buffer layer on SiC(001). (a) total charge density in the $6R3$ -SiC unit cell. (b) cross section of the total charge density along the line defined in (a). The black dots that appear when the cross section goes through the middle of an atom are due to the use of pseudopotentials (no core electrons).

F. Varchon, et al., PRB 77, 235412 (2008).

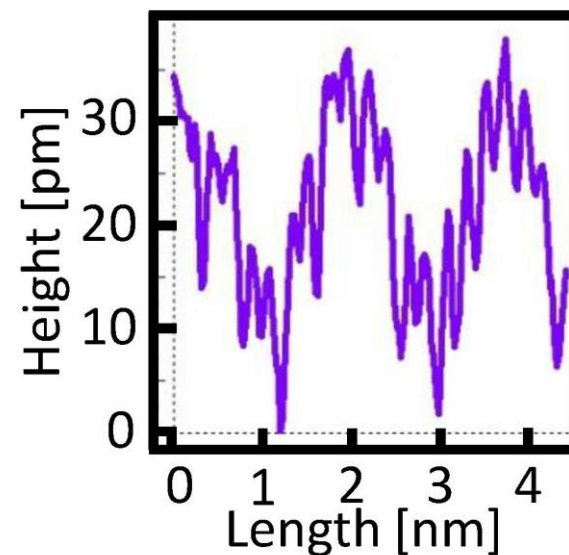
$6\sqrt{3} \times 6\sqrt{3}$ -Superstructure



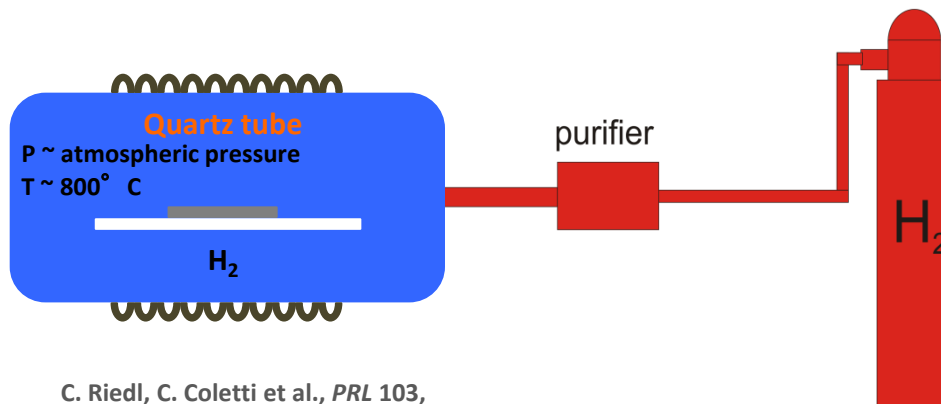
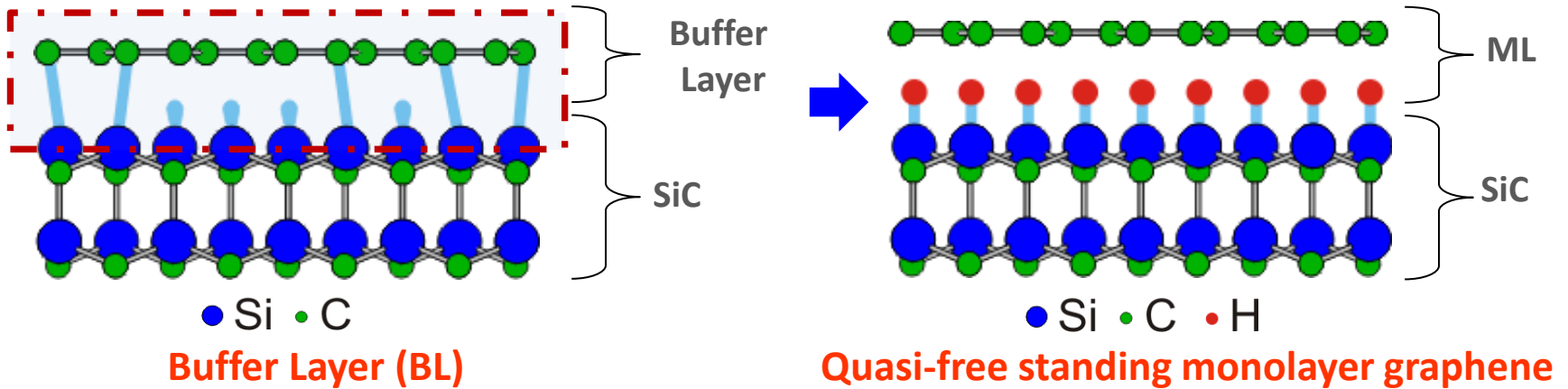
Monolayer Graphene



STM

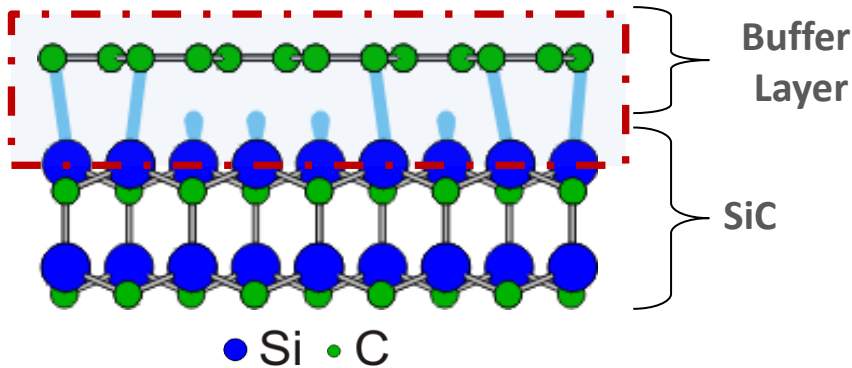


Hydrogen Intercalation

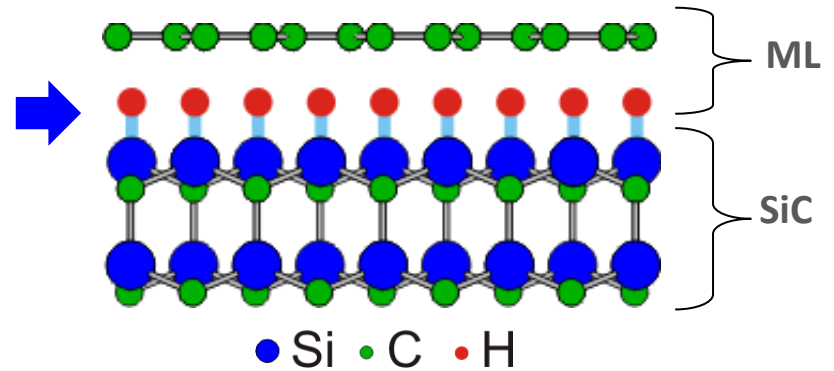
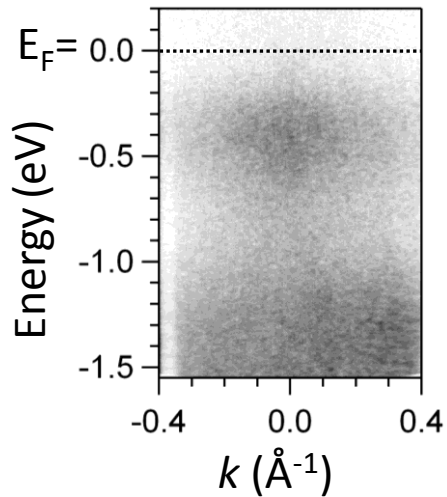


C. Riedl, C. Coletti et al., *PRL* 103, 246804 (2009)

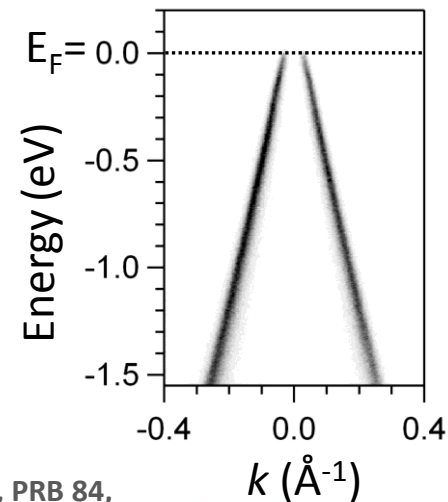
Hydrogen Intercalation



Buffer Layer (BL)



Quasi-free standing monolayer graphene

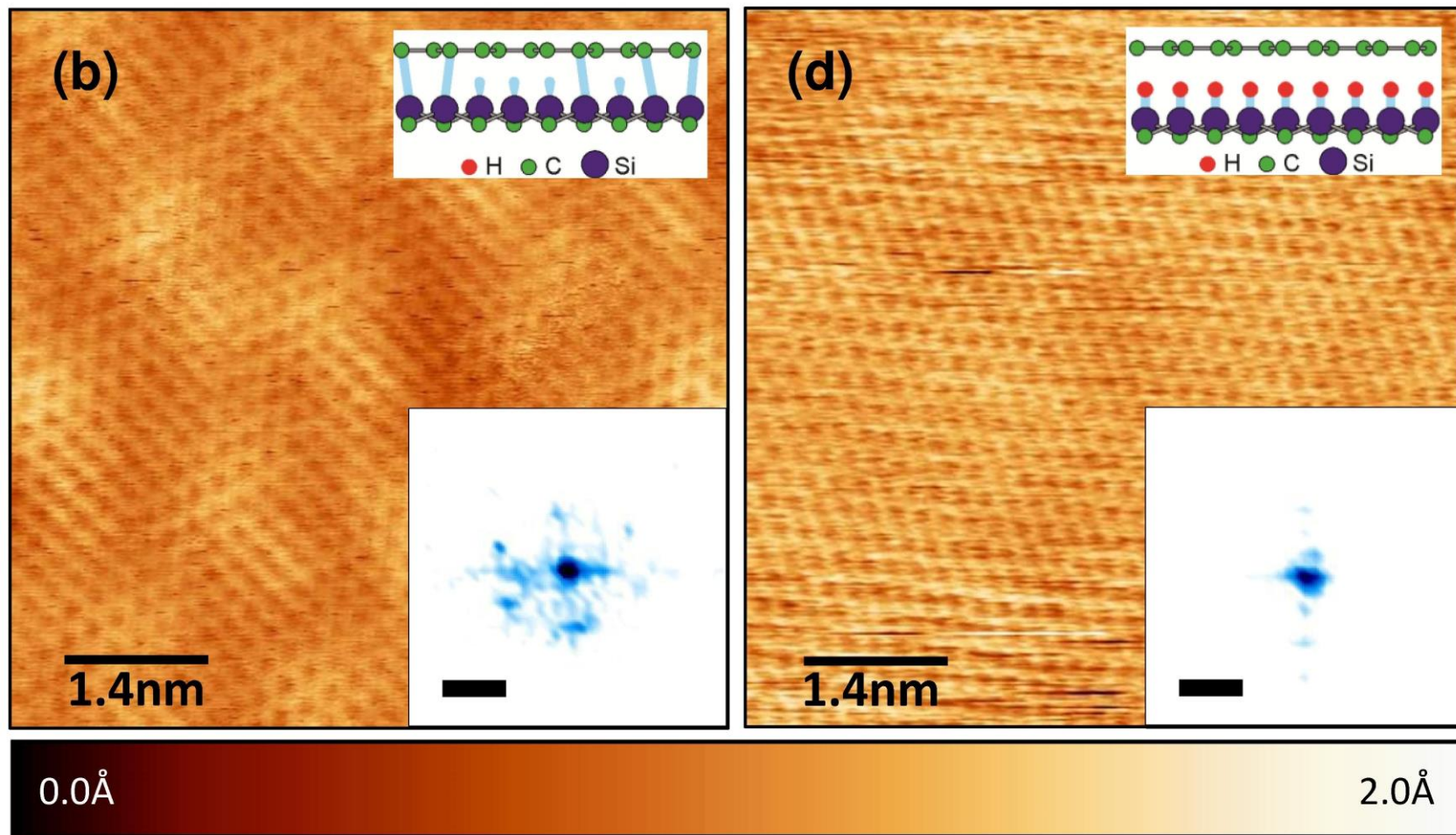


$$p = 2.6 \cdot 10^{12} \text{ cm}^{-2}$$

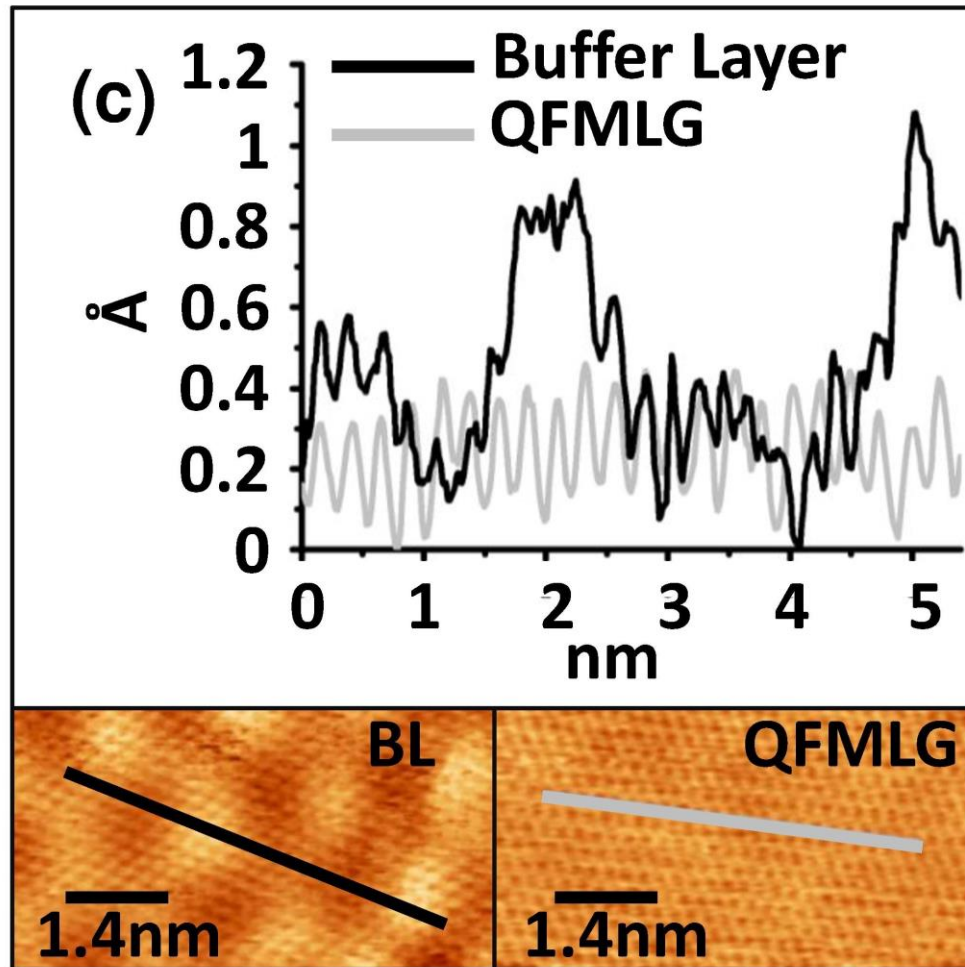
S. Forti, et al., PRB 84, 125449 (2011).

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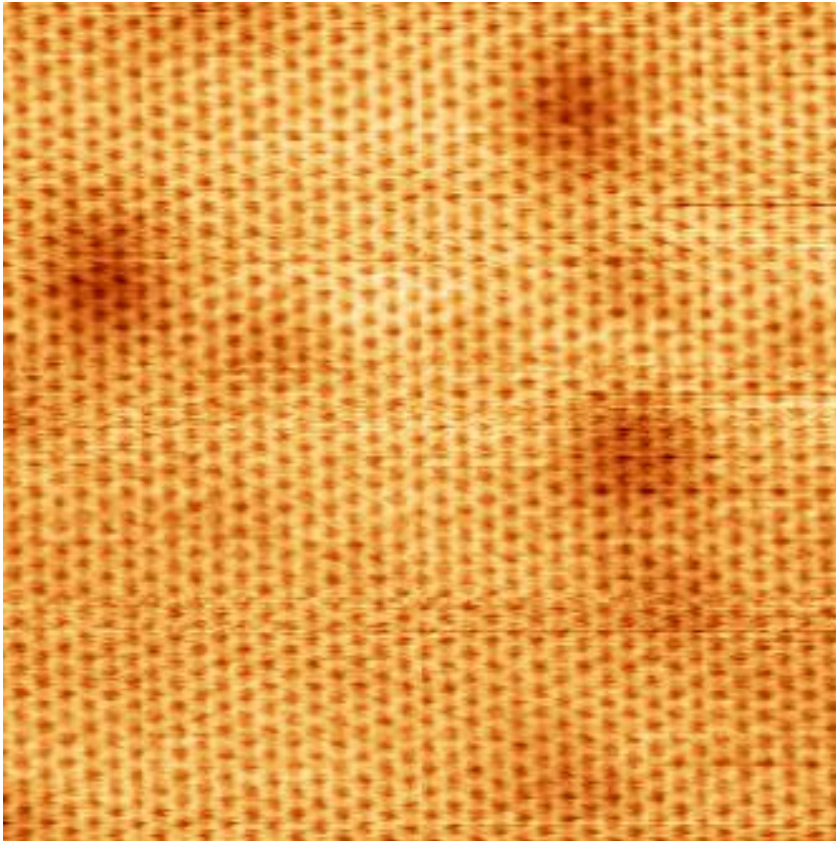
BL vs. QFMLG



BL vs. QFMLG



QFMLG



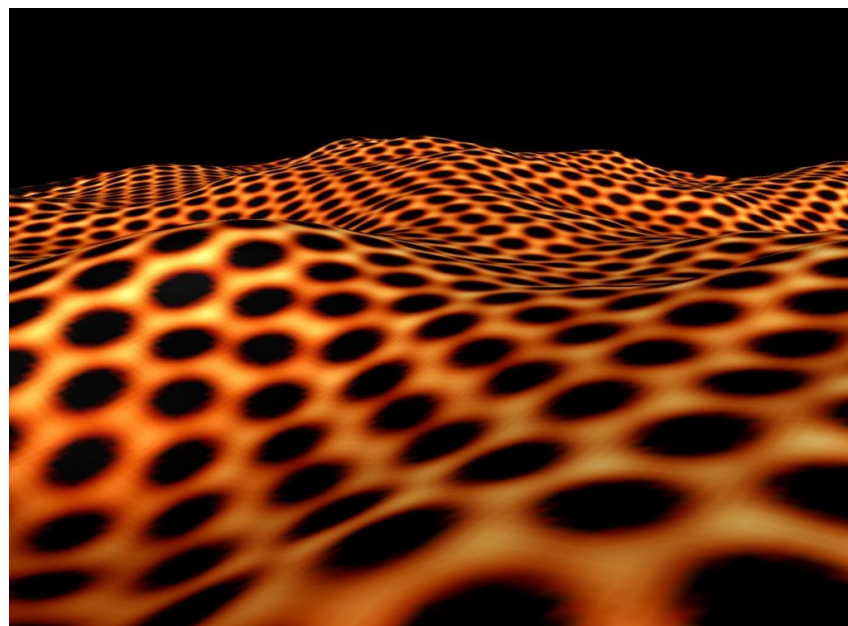
- Dangling bonds in SiC
- Contribute to carrier scattering as charged impurities
- Reduce mobility

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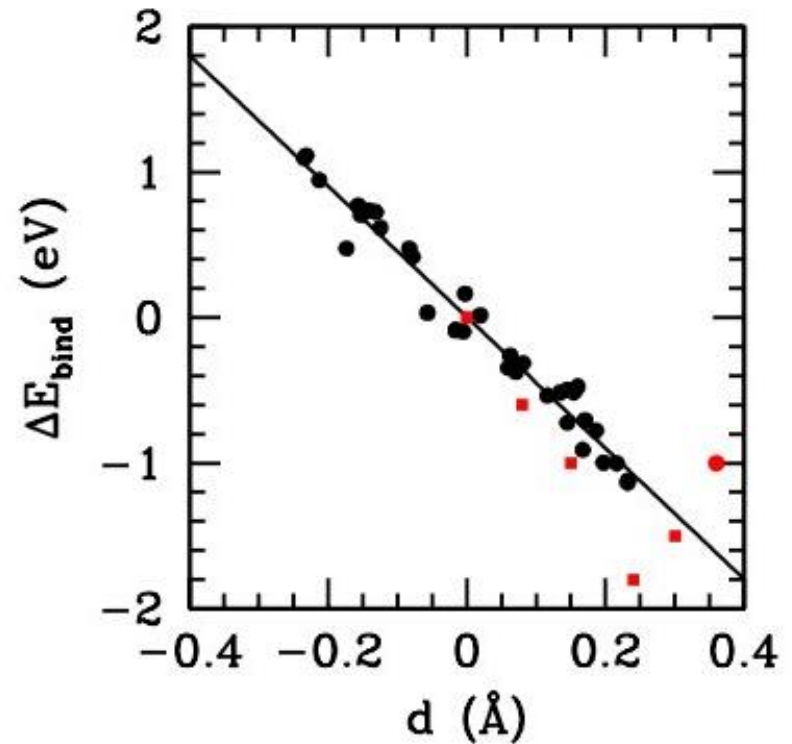
Graphene Curvature

- Exploit graphene curvature for hydrogen storage at room temperature and pressure



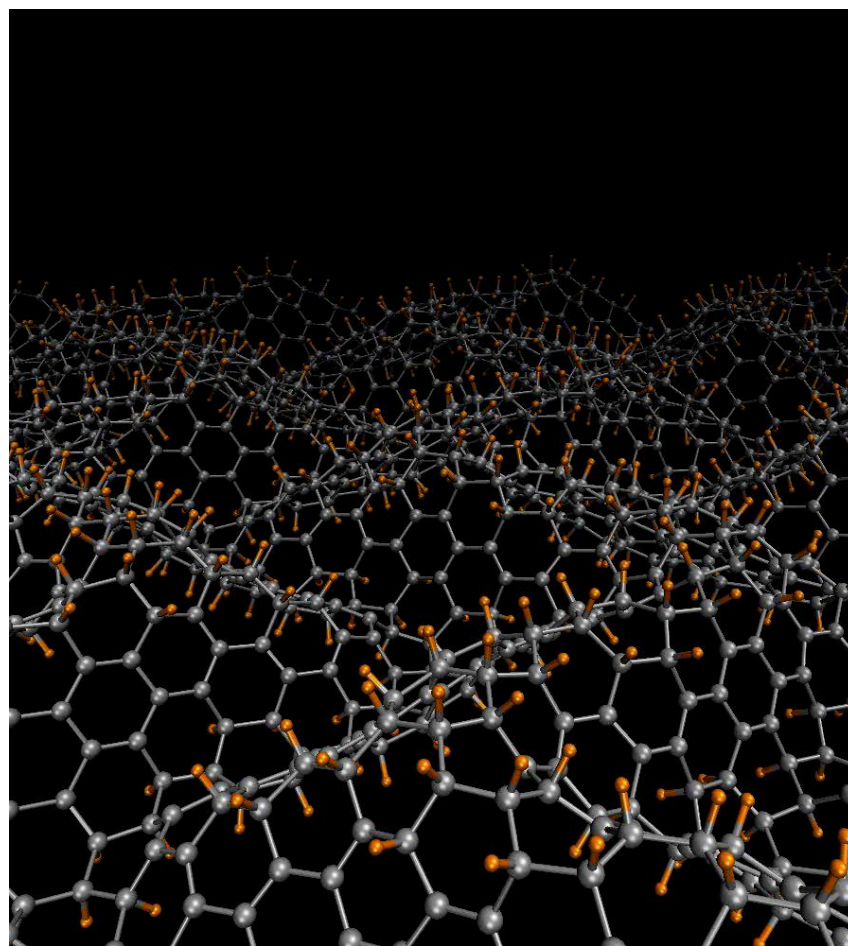
Graphene Curvature

- Exploit graphene curvature for hydrogen storage at room temperature and pressure
- The hydrogen binding energy on graphene is strongly dependent on local curvature and it is larger on convex parts

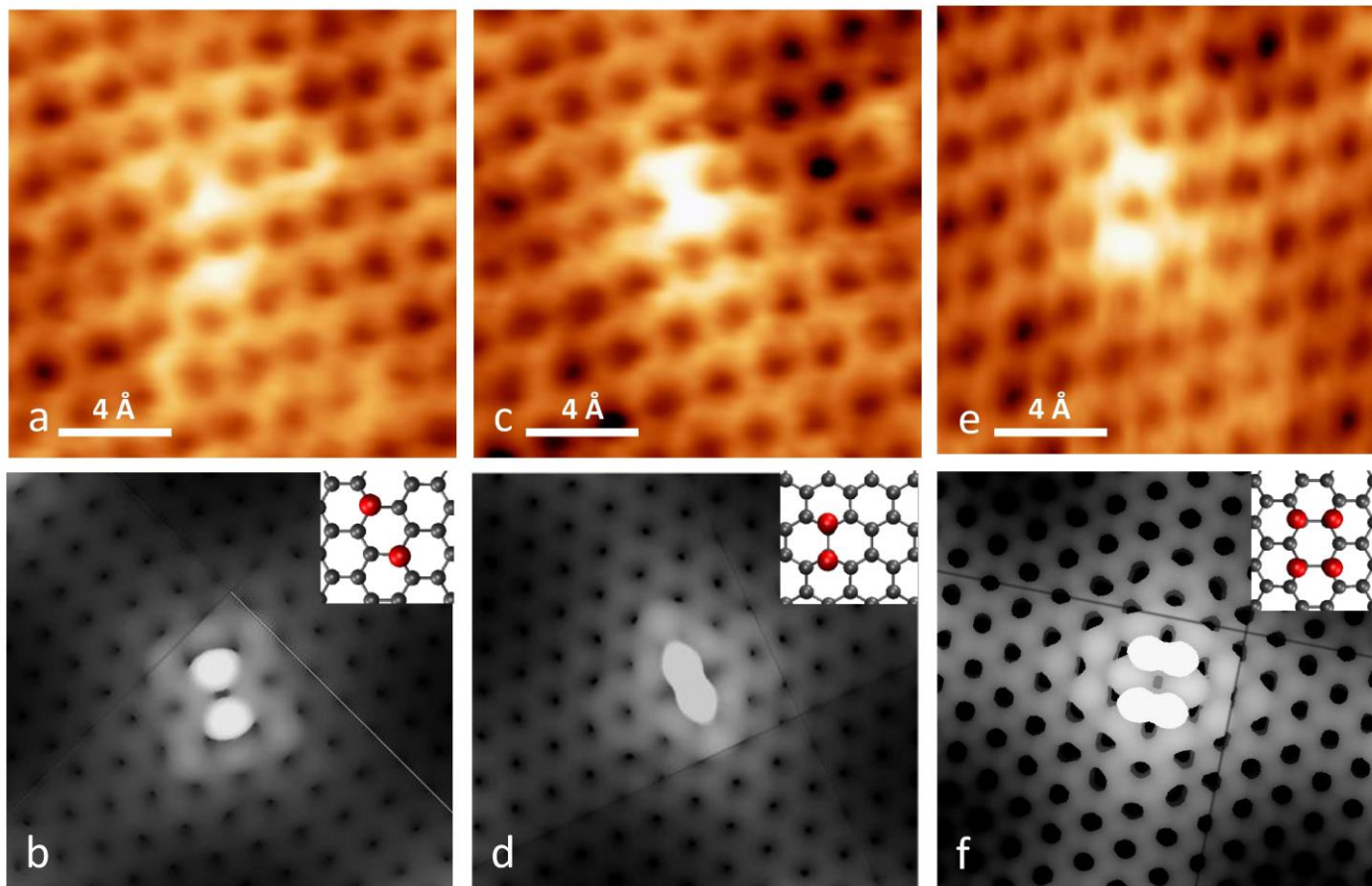


Graphene Curvature

- Exploit graphene curvature for hydrogen storage at room temperature and pressure
- The hydrogen binding energy on graphene is strongly dependent on local curvature and it is larger on convex parts
- Atomic hydrogen spontaneously sticks on convex parts; inverting curvature H is expelled



H-dimers and tetramers

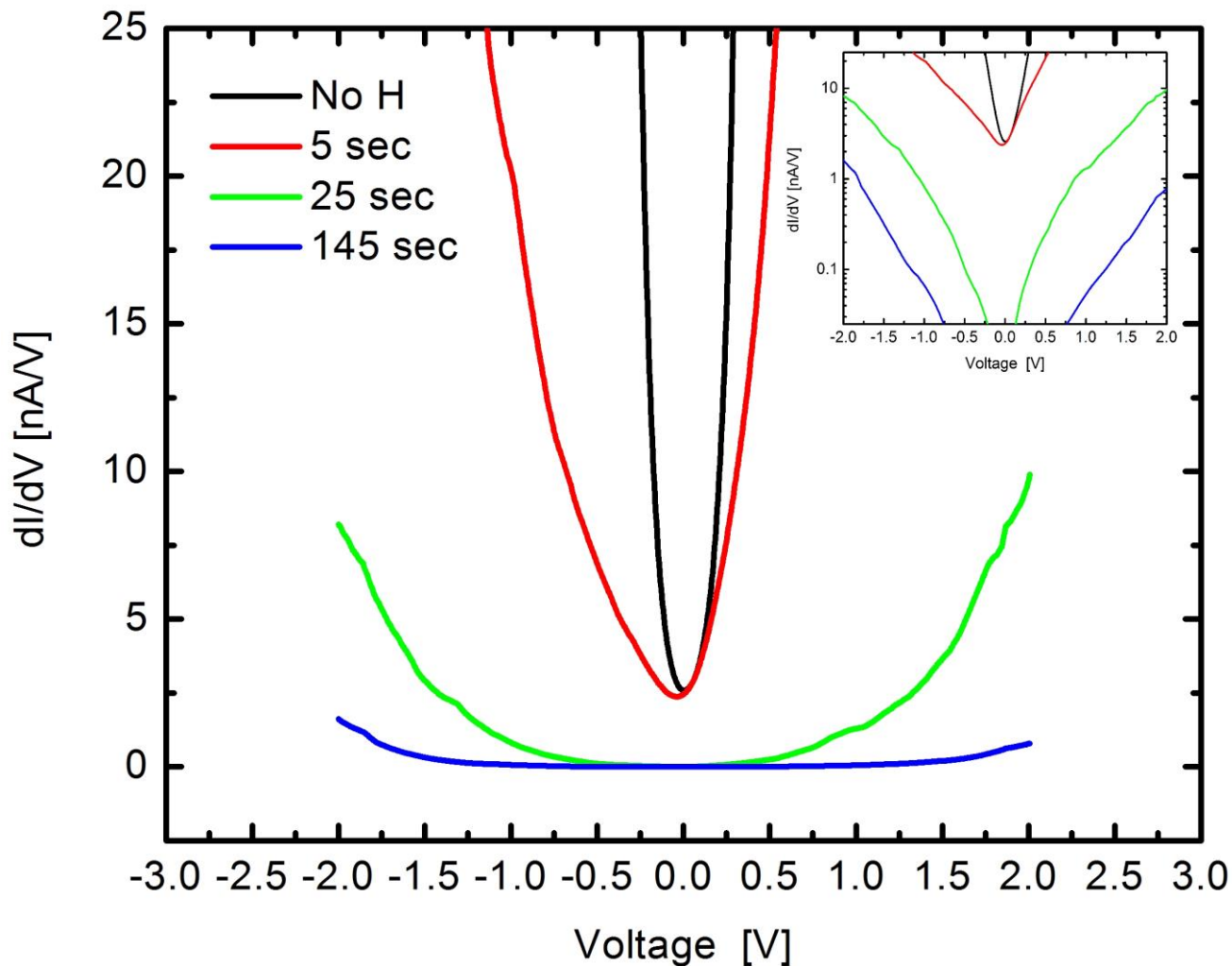


Para-dimer

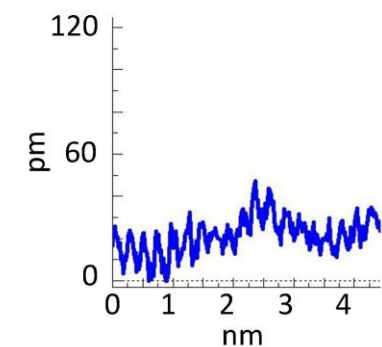
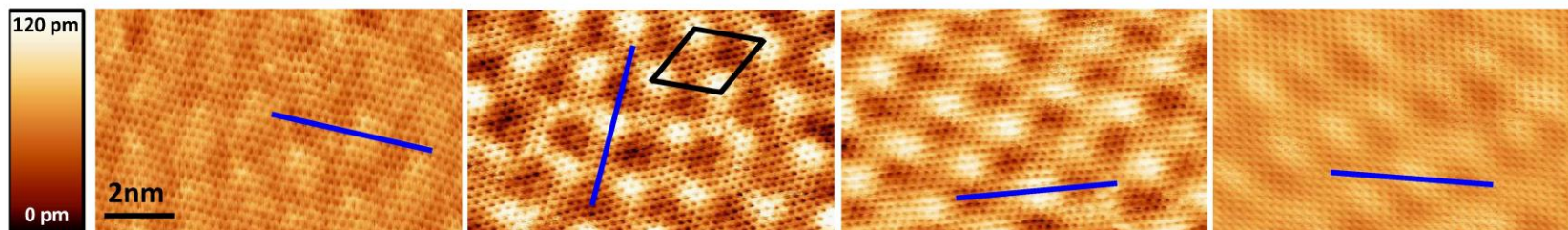
Ortho-dimer

Tetramer

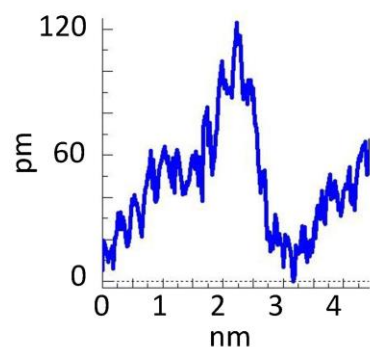
STS after hydrogenation



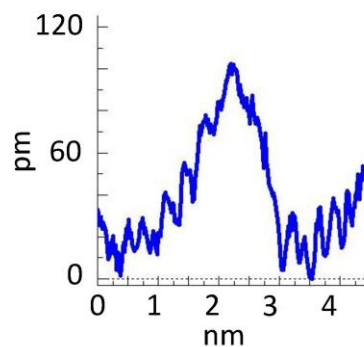
H adsorption and desorption



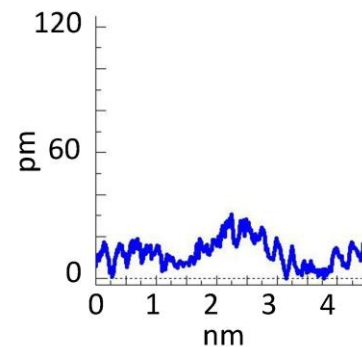
a Pristine graphene



b Hydrogenated graphene

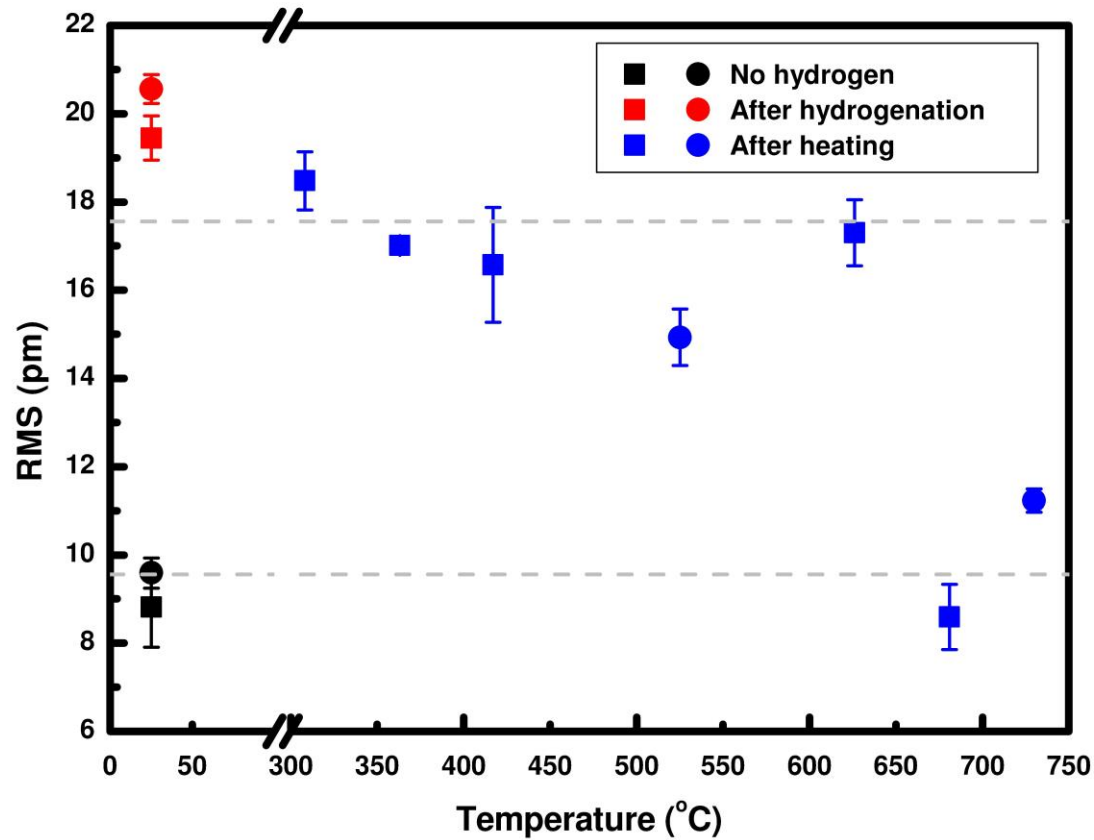


c After heating 630° C

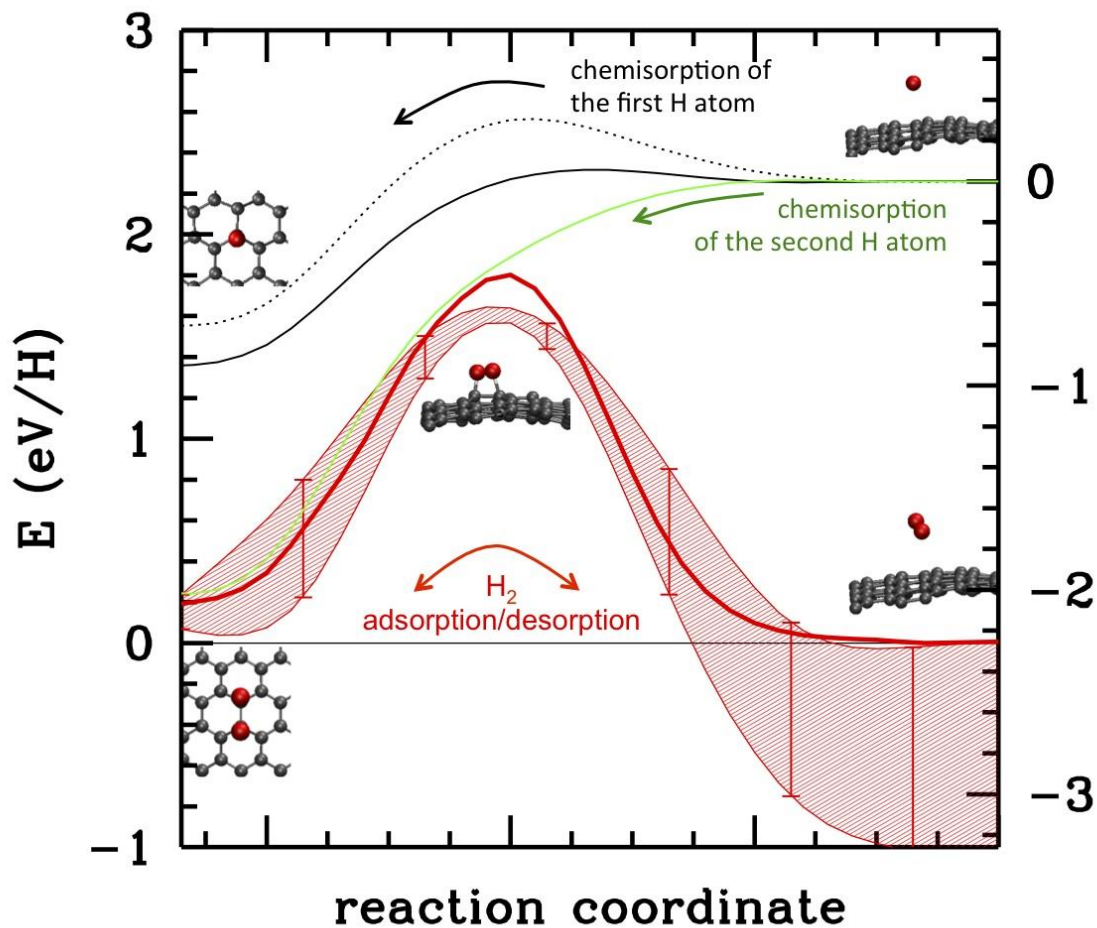


d After heating 680° C

RMS roughness



DFT calculations

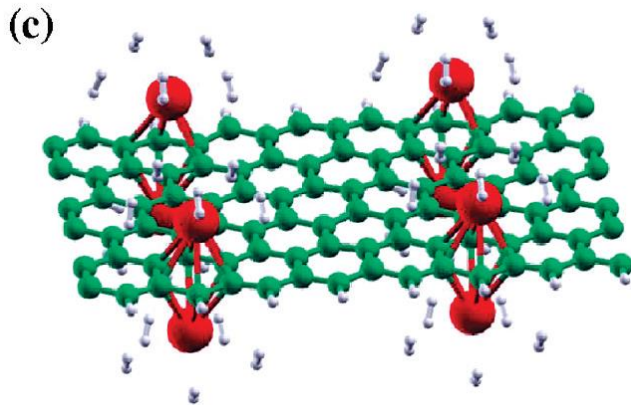


Outline

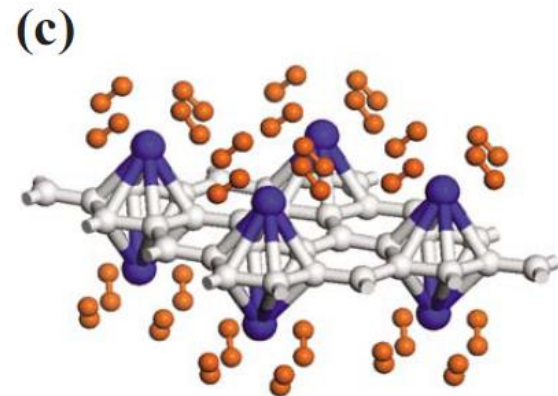
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Functionalized Graphene

- Functionalized graphene has been predicted to adsorb up to 9 wt% of hydrogen
- Modify graphene with various chemical species, such as calcium or transition metals (Titanium)

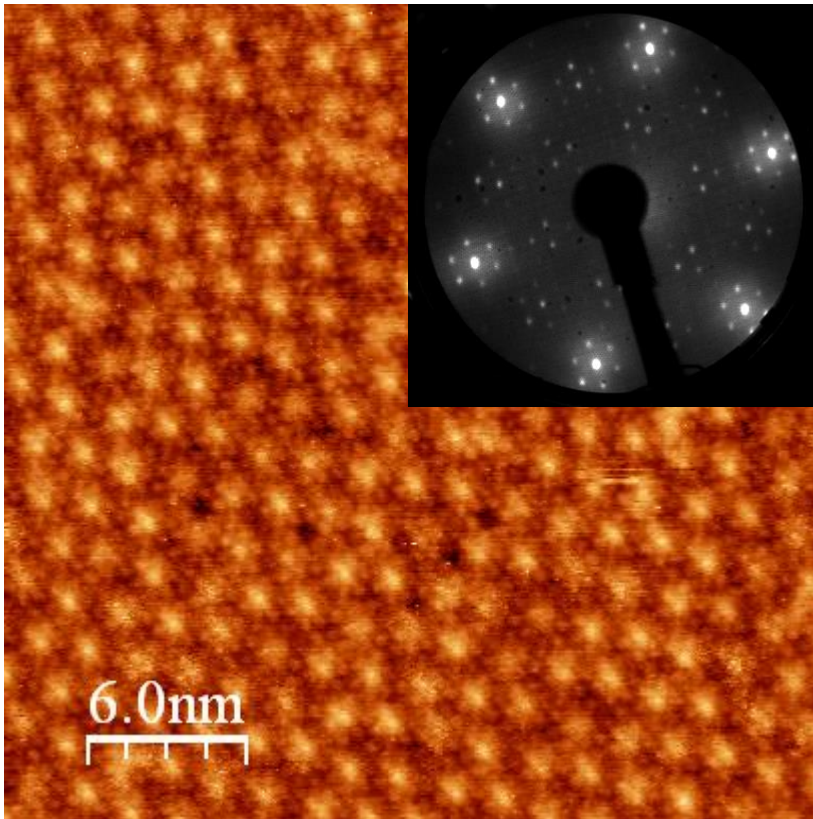


Lee et al., Nano Lett. 10 (2010) 793

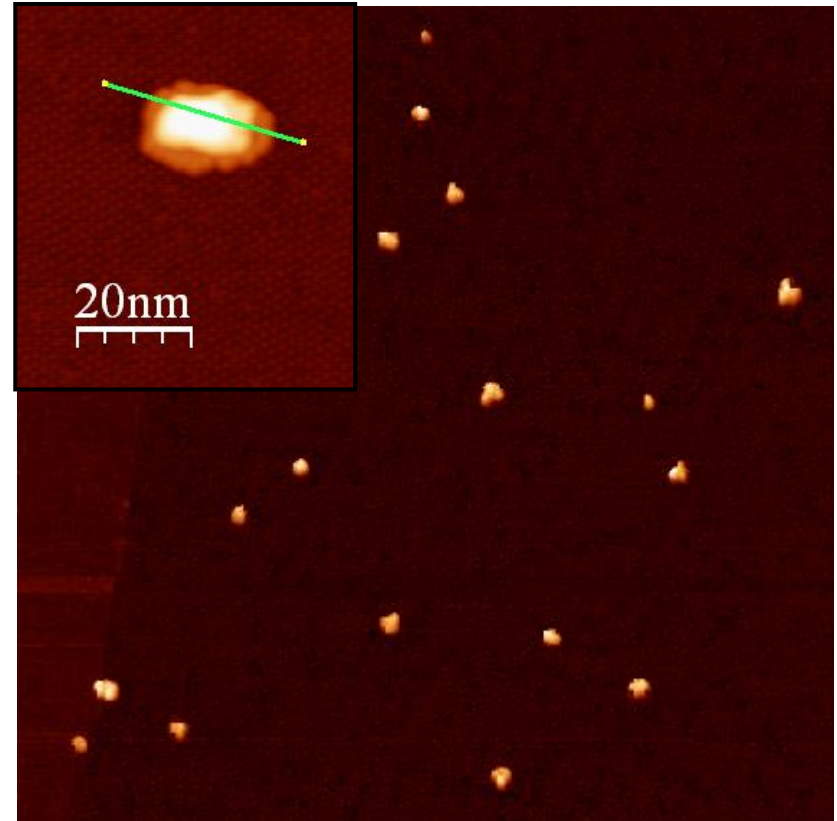


Durgen et al., PRB 77 (2007) 085405

Titanium on graphene

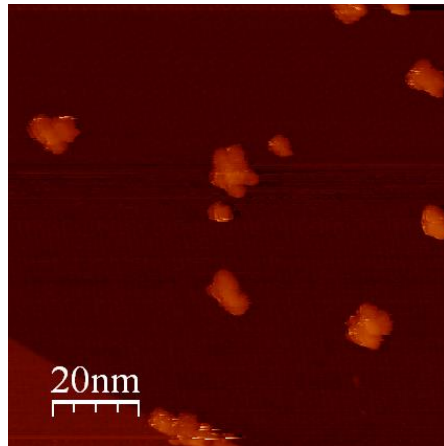


ML graphene on SiC(0001)
with reconstruction

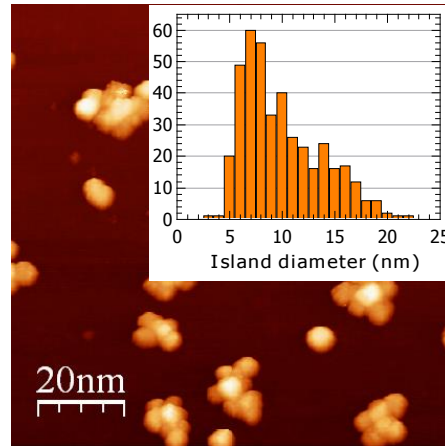


After deposition of Ti at RT

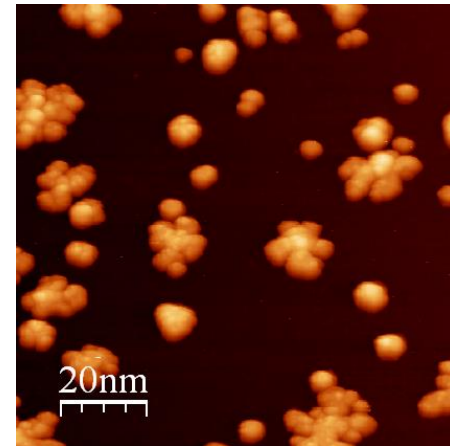
Titanium island growth



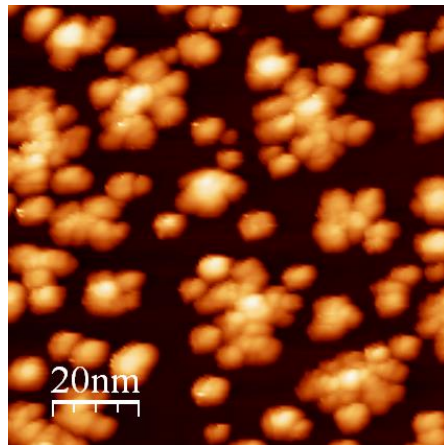
6% Coverage



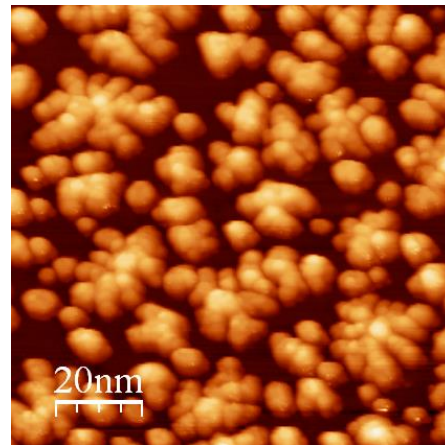
16% Coverage



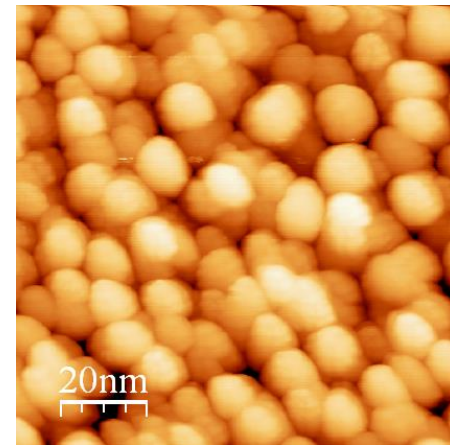
29% Coverage



53% Coverage



79% Coverage

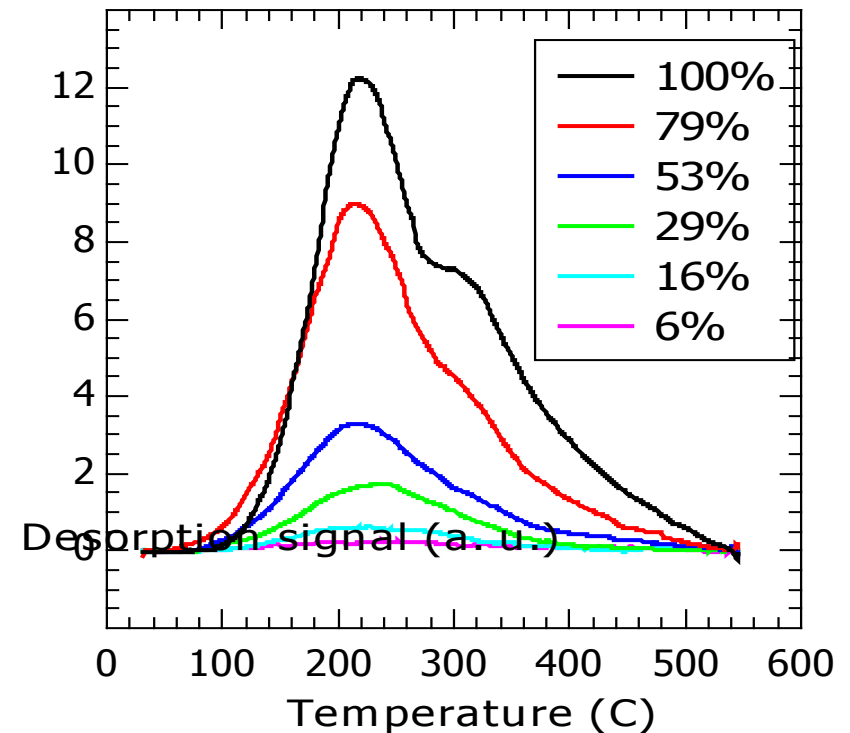


100% Coverage

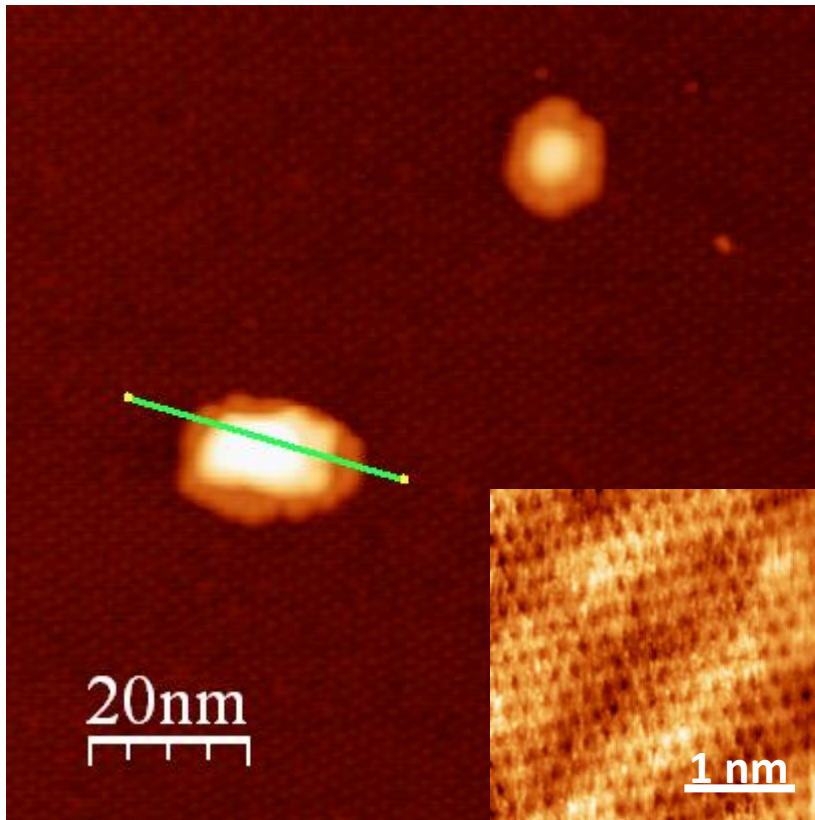
Thermal desorption spectroscopy

- Deposition of different amounts of Titanium
- Offering Hydrogen (D_2)
- (1×10^{-7} mbar for 5 min)
- Heating sample with constant rate (10K/s) up to $550^\circ C$
- Measuring mass-sensitive desorption with a mass spectrometer

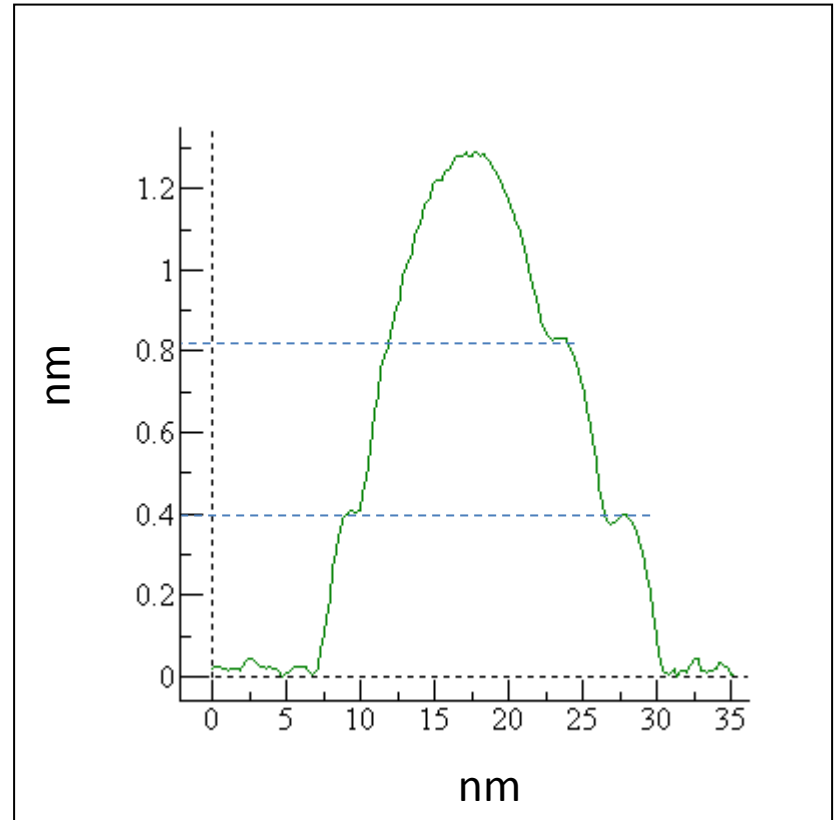
Spectra for different Ti-coverages



Forming of Islands



100 nm, 1 V, 82 pA



Hydrogen adsorption capacity of adatoms on double carbon vacancies of graphene: A trend study from first principles

K. M. Fair,^{1,2} X. Y. Cui,^{3,4,*} L. Li,¹ C. C. Shieh,¹ R. K. Zheng,^{1,3} Z. W. Liu,^{3,5} B. Delley,⁶ M. J. Ford,²
S. P. Ringer,^{3,4} and C. Stampfl^{1,7}

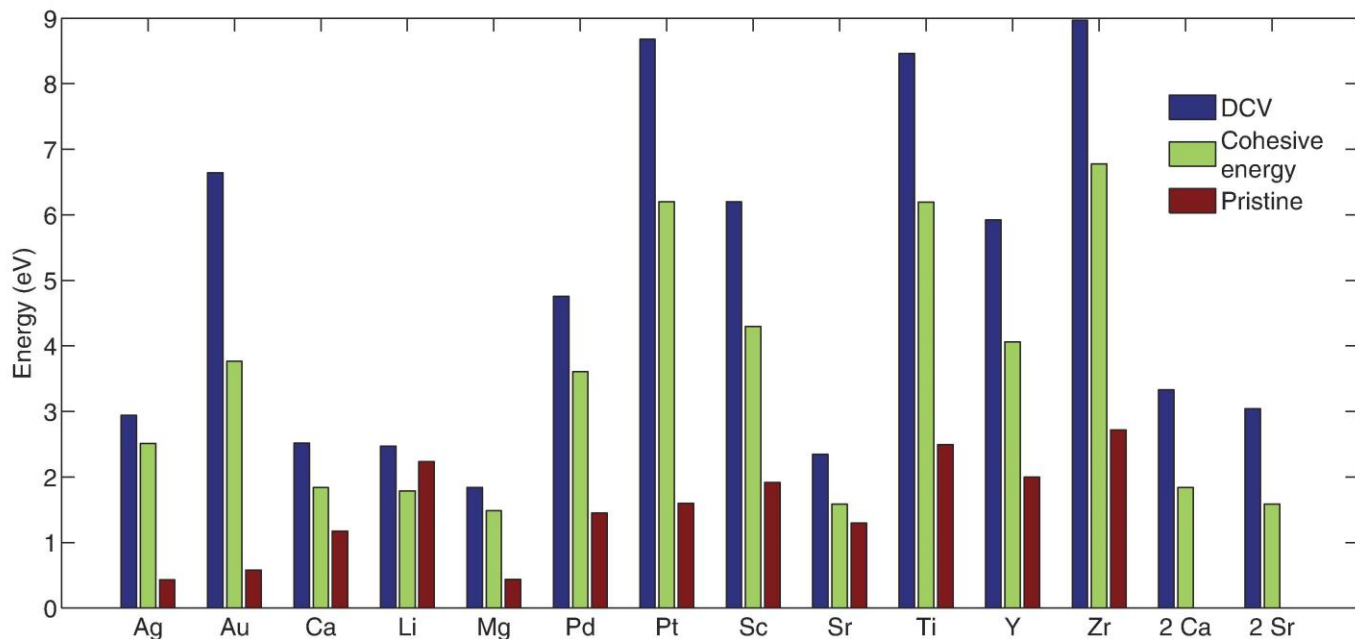
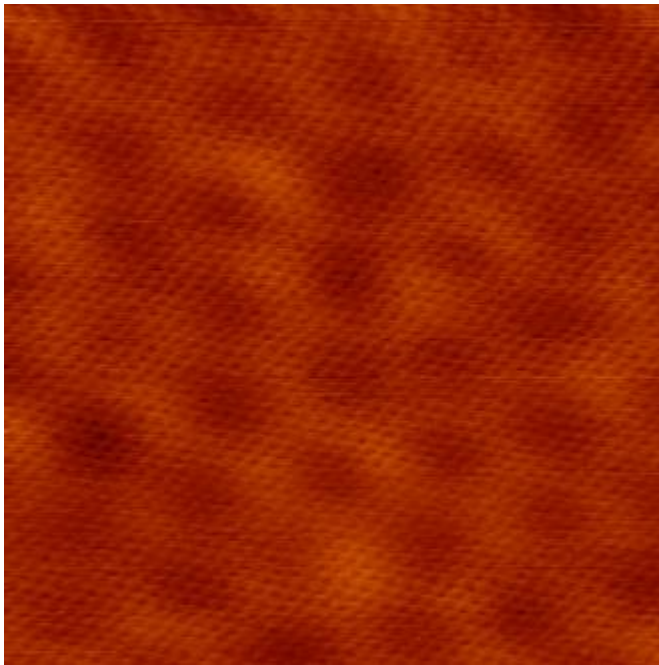


FIG. 1. (Color online) The binding energy of adatoms to graphene DCVs (blue), and pristine graphene (red), as well as the cohesive energy of the respective metal (green). Also included are the binding energies per adatom of two Ca and Sr (“2Ca” and “2Sr”) adatoms with one on either side of the DCV.

DCV = Double Carbon Vacancy

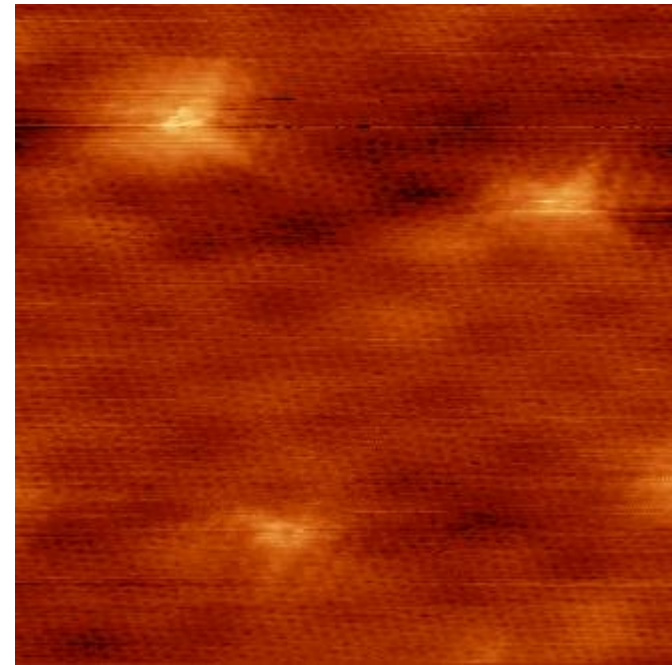
N₂ - sputtering of the graphene surface

Clean graphene surface



10x10 nm², 1V, 0.8nA

Sputtered 150s @100eV

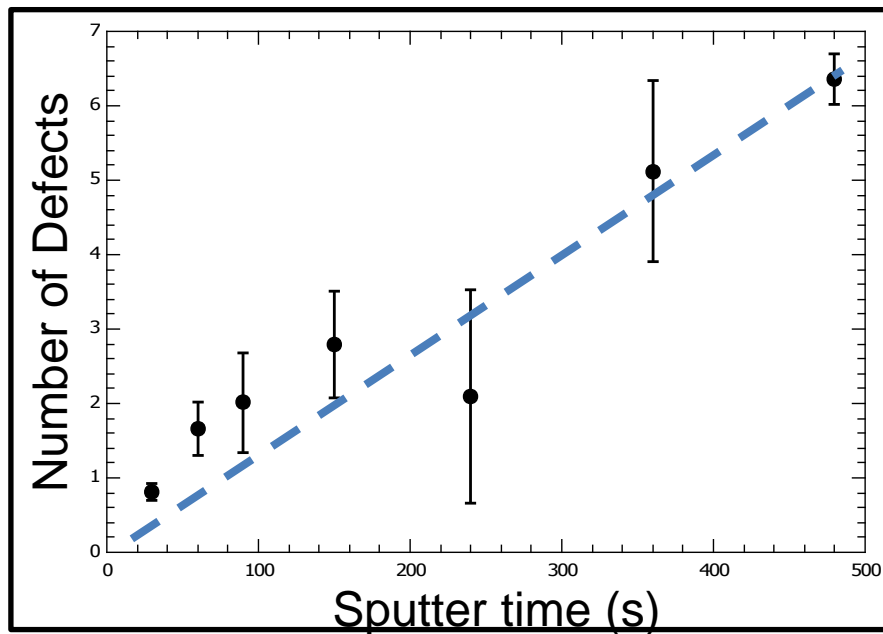


10x10 nm², 1V, 0.8nA

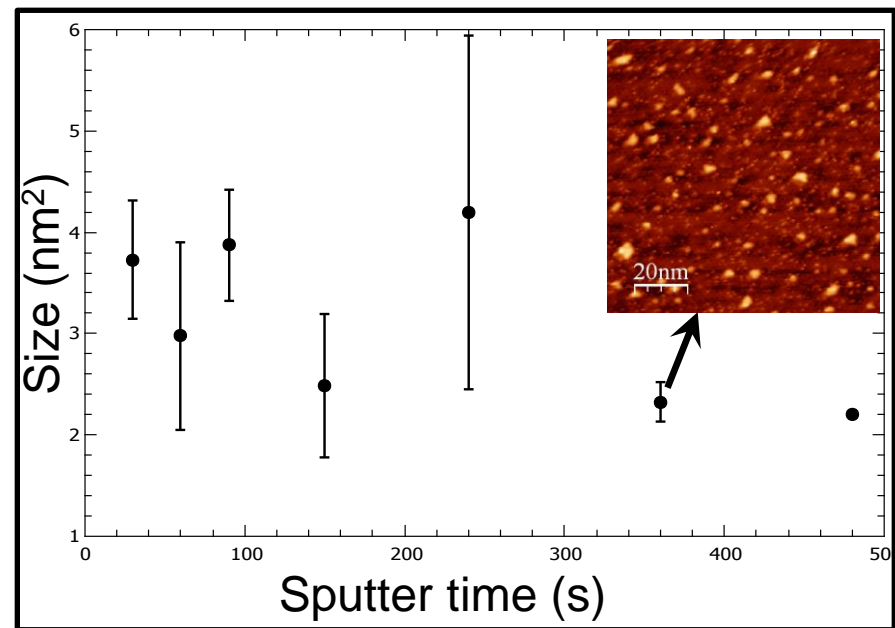
Defects in the graphene film should reduce the mobility of Ti-atoms and lead to more and smaller islands.

Distribution of defects in graphene

Number of Defects per 100nm²

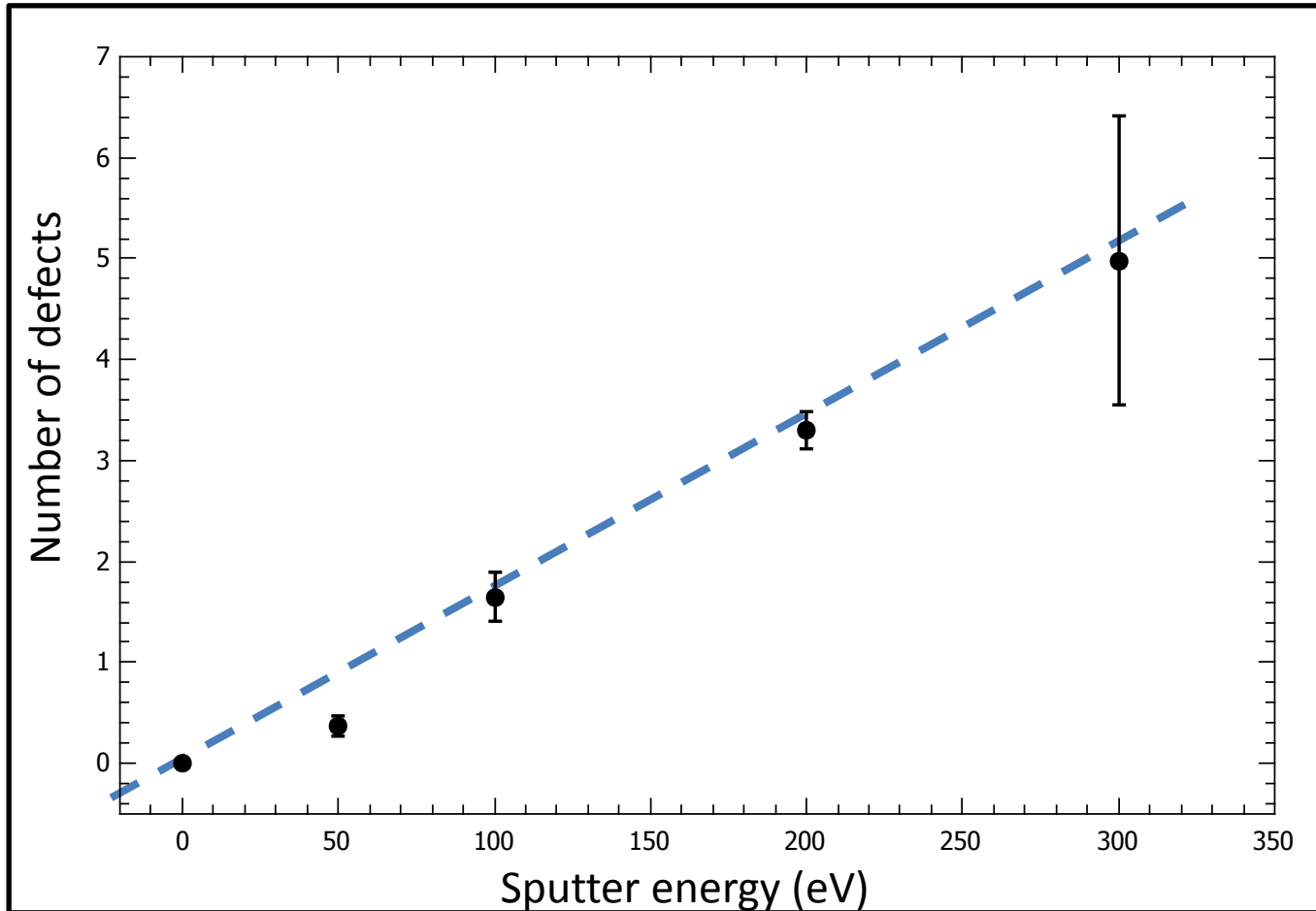


Average size of defects



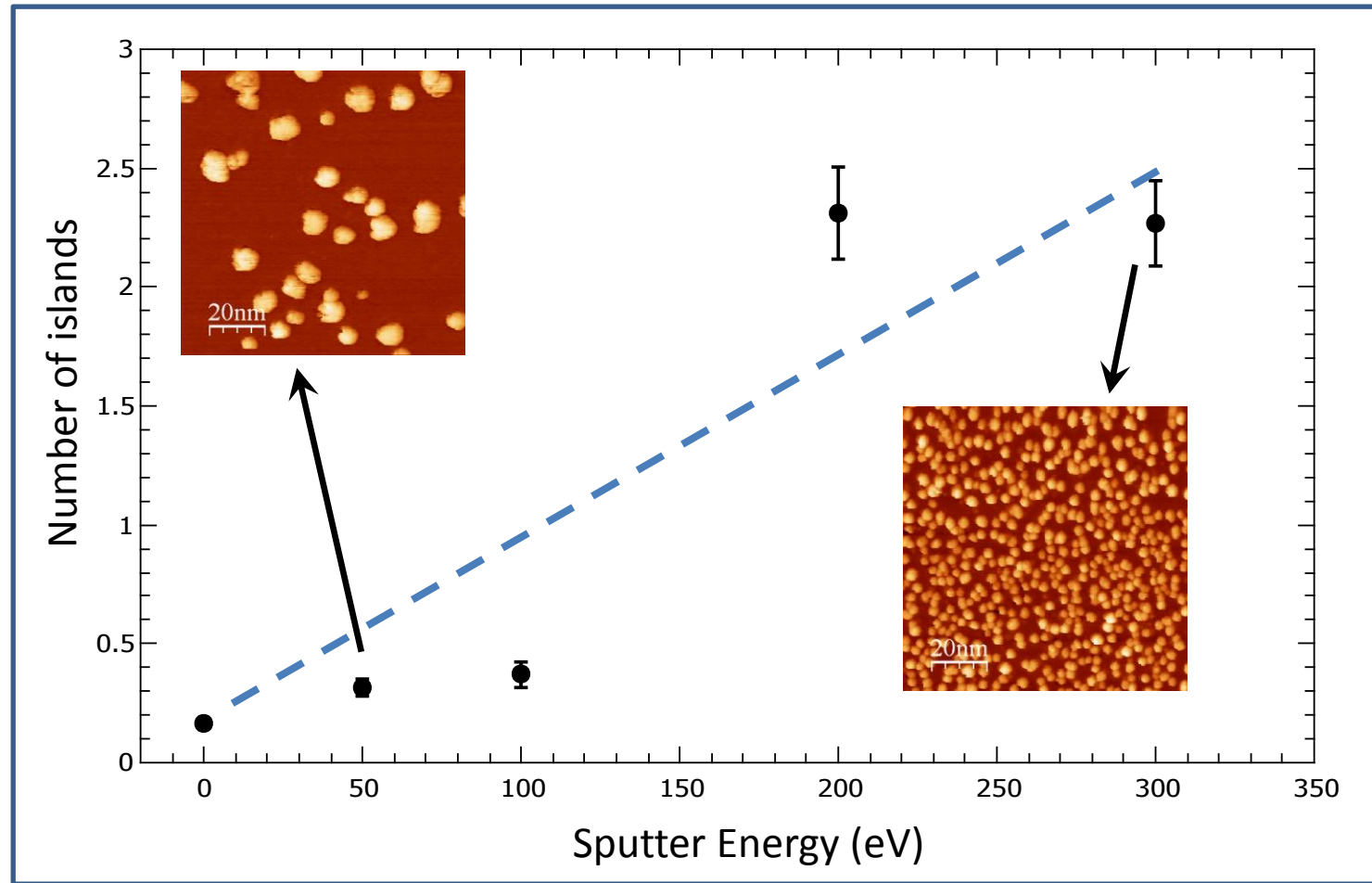
Energy: 200eV, Ion Current: (5.7 +/- 1) nA

Average number of induced defects per 100nm²



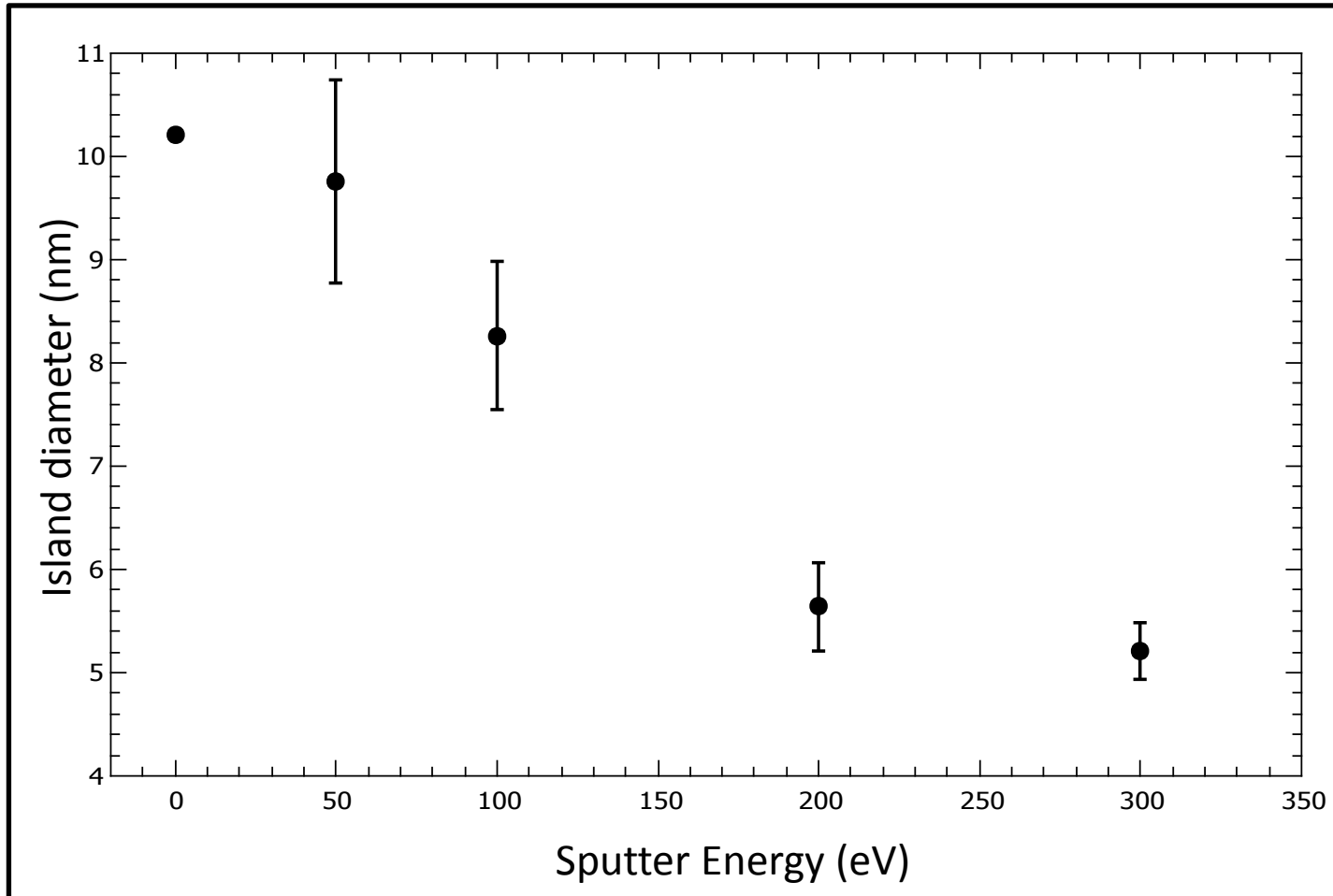
Sputter time: 150s

Average Number of Islands per 100 nm²

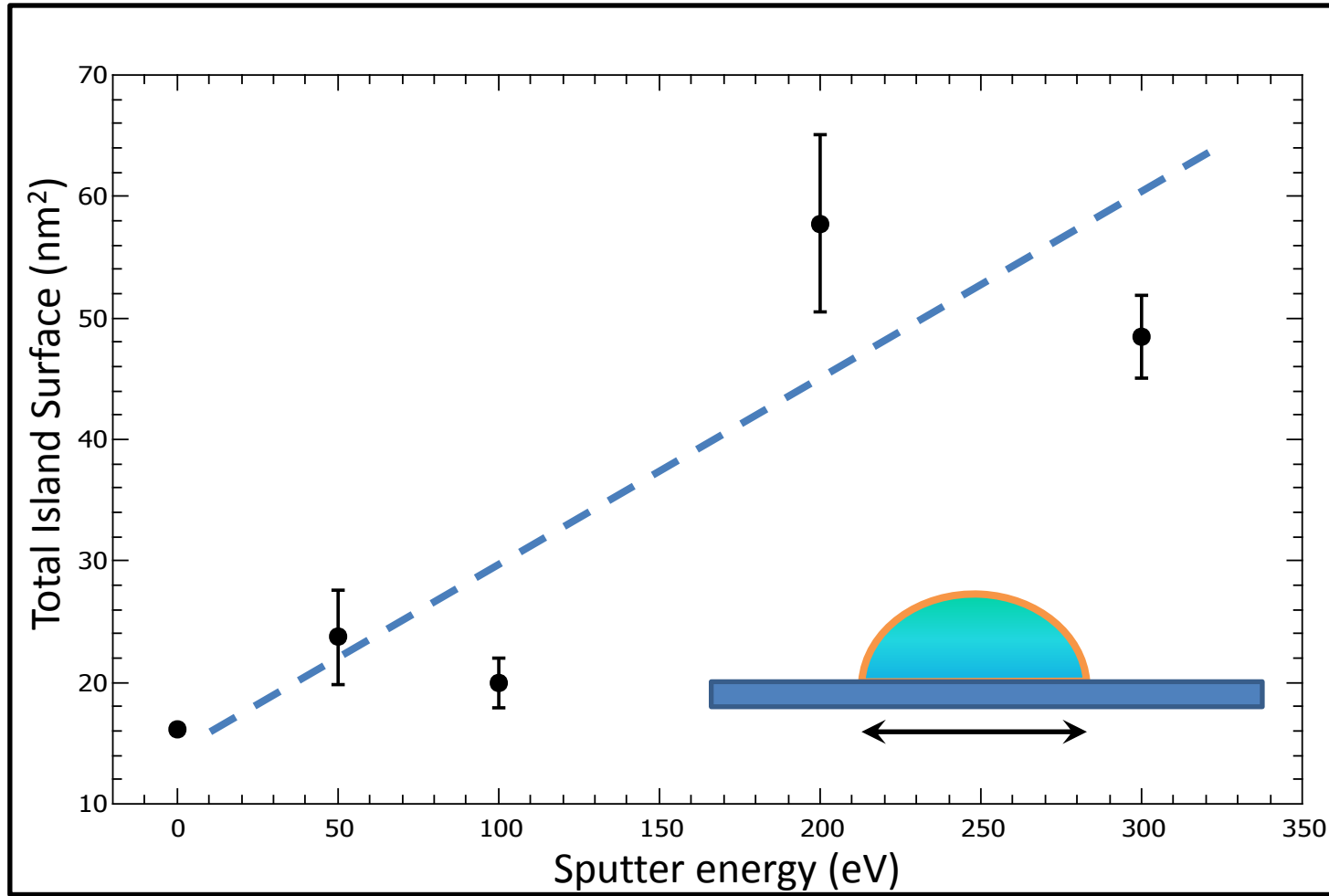


Sputtered 150 s and Deposition of 0.5 ML Titanium

Average diameter of individual Ti-Islands



“Active” 3D-surface per 100nm²



Conclusions

- Graphene is a promising material for hydrogen storage
- Curvature-dependent adsorption and desorption of hydrogen
 - reusable hydrogen storage devices that do not depend on temperature or pressure changes.
- Graphene functionalized by Ti:
 - Stability of hydrogen binding at room temperature
 - Hydrogen desorbes at moderate temperatures
 - Modifying the size and distribution of Islands by sputtering and increasing the active surface



Coauthors



S. Goler



T. Mashoff



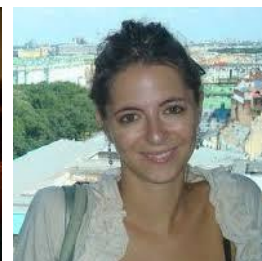
Y. Murata



D. Convertino



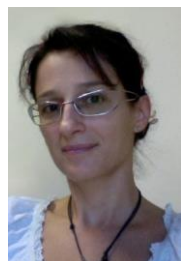
V. Miseikis



C. Coletti



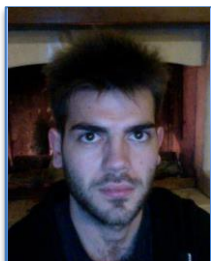
V. Piazza



V. Tozzini



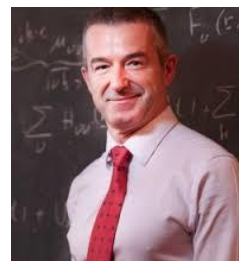
P. Pingue



F. Colangelo



V. Pellegrini



F. Beltram



K. V. Emtsev, U. Starke,
S. Forti



M. Takamura



S. Tanabe



H. Hibino



Funding





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FASSA®

National Enterprise for nanoScience and nanoTechnology

NEST

18th European
Molecular Beam Epitaxy
March 15-18, 2015
Canazei (IT)
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Abstract deadline:
November 1, 2014

Topics:

Epitaxy of III-N materials (GaN, InN, AlN)
Semiconductor Quantum Wires and 3D growth
Novel III-V heterostructures including dilute nitrides and bismides
Epitaxy of oxides
Epitaxy of ferromagnetic and spintronic materials
Nanostructures, site-controlled epitaxy, and droplet epitaxy
Epitaxy of novel materials
Characterization of epitaxial materials
Epitaxy of heterostructures for applications in photovoltaics, electronics, and optoelectronics
MBE production technology

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